LMV321-N/LMV321-N-Q1/LMV358-N/LMV358-N-Q1/LMV324-N/LMV324-N-Q1 Single/Dual/Quad General Purpose, Low Voltage, Rail-to-Rail Output Operational Amplifiers

Check for Samples: LMV321-N, LMV321-N-Q1, LMV358-N, LMV358-N-Q1, LMV324-N, LMV324-N-Q1

FEATURES

- **(For V^+ = 5V and V^- = 0V, unless otherwise specified)**
- **LMV321-N, LMV358-N, and LMV324-N are available in Automotive AEC-Q100 Grade 1 & 3 versions**
- **Guaranteed 2.7V and 5V performance**
- **No crossover distortion**
- **Industrial temperature range −40°C to +125°C**
- **Gain-bandwidth product 1 MHz**
- **Low supply current**
- **LMV321-N 130 µA**
- **LMV358-N 210 µA**
- **LMV324-N 410 µA**
- **Rail-to-rail output swing @ 10 kΩ V^+− 10 mV & V^-+ 65 mV**
- **V_{CM} Range −0.2V to V^+− 0.8V**

APPLICATIONS

- **Active filters**
- **General purpose low voltage applications**
- **General purpose portable devices**

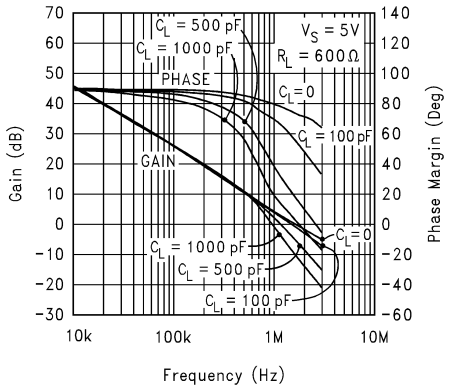
DESCRIPTION

The LMV358-N/LMV324-N are low voltage (2.7V to 5.5V) versions of the dual and quad commodity op amps LM358/LM324 (5V to 30V). The LMV321-N is the single channel version. The LMV321-N/LMV358-N/LMV324-N are the most cost effective solutions for applications where low voltage operation, space efficiency, and low price are important. They offer specifications that meet or exceed the familiar LM358/LM324. The LMV321-N/LMV358-N/LMV324-N have rail-to-rail output swing capability and the input common-mode voltage range includes ground. They all exhibit excellent speed to power ratio, achieving 1 MHz of bandwidth and 1 V/µs slew rate with low supply current.

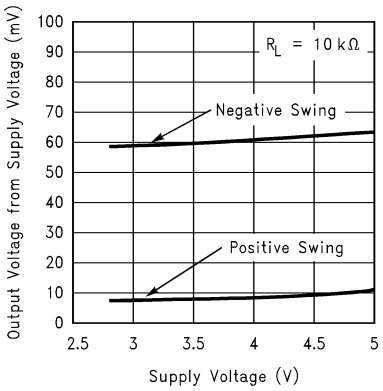
The LMV321-N is available in the space saving 5-Pin SC70, which is approximately half the size of the 5-Pin SOT23. The small package saves space on PC boards and enables the design of small portable electronic devices. It also allows the designer to place the device closer to the signal source to reduce noise pickup and increase signal integrity.

The chips are built with Texas Instruments's advanced submicron silicon-gate BiCMOS process. The LMV321-N/LMV358-N/LMV324-N have bipolar input and output stages for improved noise performance and higher output current drive.

Gain and Phase vs. Capacitive Load



Output Voltage Swing vs. Supply Voltage



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings (1)(2)

ESD Tolerance (3)	
Human Body Model	
LMV358-N/LMV324-N	2000V
LMV321-N	900V
Machine Model	100V
Differential Input Voltage	±Supply Voltage
Input Voltage	−0.3V to +Supply Voltage
Supply Voltage (V^+–V^-)	5.5V
Output Short Circuit to V^+	(4)
Output Short Circuit to V^-	(5)
Soldering Information	
Infrared or Convection (30 sec)	260°C
Storage Temp. Range	−65°C to 150°C
Junction Temperature (6)	150°C

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.
(2) **If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office / Distributors for availability and specifications.**
(3) Human Body Model, applicable std. MIL-STD-883, Method 3015.7. Machine Model, applicable std. JESD22-A115-A (ESD MM std. of JEDEC)Field-Induced Charge-Device Model, applicable std. JESD22-C101-C (ESD FICDM std. of JEDEC
(4) Shorting output to V^+ will adversely affect reliability.
(5) Shorting output to V^-will adversely affect reliability.
(6) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA}. The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} – T_A)/ \theta_{JA}$. All numbers apply for packages soldered directly onto a PC Board.

Operating Ratings (1)

Supply Voltage	2.7V to 5.5V
Temperature Range (2)	
LMV321-N/LMV358-N/LMV324-N	−40°C to +125°C
Thermal Resistance (θ_{JA}) (3)	
5-pin SC70	478°C/W
5-pin SOT23	265°C/W
8-Pin SOIC	190°C/W
8-Pin MSOP	235°C/W
14-Pin SOIC	145°C/W
14-Pin TSSOP	155°C/W

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.
(2) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA}. The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} – T_A)/ \theta_{JA}$. All numbers apply for packages soldered directly onto a PC Board.
(3) All numbers are typical, and apply for packages soldered directly onto a PC board in still air.

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2.7V DC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for T_J = 25°C, V^+ = 2.7V, V^- = 0V, V_{CM} = 1.0V, V_O = V^+/2 and R_L > 1 MΩ.

Symbol	Parameter	Conditions	Min (1)	Typ (2)	Max (1)	Units
V_{OS}	Input Offset Voltage			1.7	7	mV
TCV_{OS}	Input Offset Voltage Average Drift			5		µV/°C
I_B	Input Bias Current			11	250	nA
I_{OS}	Input Offset Current			5	50	nA
CMRR	Common Mode Rejection Ratio	0V ≤ V_{CM} ≤ 1.7V	50	63		dB
PSRR	Power Supply Rejection Ratio	2.7V ≤ V^+ ≤ 5V V_O = 1V	50	60		dB
V_{CM}	Input Common-Mode Voltage Range	For CMRR ≥ 50 dB	0	−0.2		V
				1.9	1.7	V
V_O	Output Swing	R_L = 10 kΩ to 1.35V	V^+ −100	V^+ −10		mV
				60	180	mV
I_S	Supply Current	LMV321-N		80	170	µA
		LMV358-N Both amplifiers		140	340	µA
		LMV324-N All four amplifiers		260	680	µA

(1) All limits are guaranteed by testing or statistical analysis.
(2) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not guaranteed on shipped production material.

2.7V AC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for T_J = 25°C, V^+ = 2.7V, V^- = 0V, V_{CM} = 1.0V, V_O = V^+/2 and R_L > 1 MΩ.

Symbol	Parameter	Conditions	Min (1)	Typ (2)	Max (1)	Units
GBWP	Gain-Bandwidth Product	C_L = 200 pF		1		MHz
Φ_m	Phase Margin			60		Deg
G_m	Gain Margin			10		dB
e_n	Input-Referred Voltage Noise	f = 1 kHz		46		$\frac{nV}{\sqrt{Hz}}$
i_n	Input-Referred Current Noise	f = 1 kHz		0.17		$\frac{pA}{\sqrt{Hz}}$

(1) All limits are guaranteed by testing or statistical analysis.
(2) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not guaranteed on shipped production material.

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5V DC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for T_J = 25°C, V^+ = 5V, V^- = 0V, V_{CM} = 2.0V, V_O = V^+/2 and R_L > 1 MΩ. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (1)	Typ (2)	Max (1)	Units
V_{OS}	Input Offset Voltage			1.7	7 **9**	mV
TCV_{OS}	Input Offset Voltage Average Drift			5		µV/°C
I_B	Input Bias Current			15	250 **500**	nA
I_{OS}	Input Offset Current			5	50 **150**	nA
CMRR	Common Mode Rejection Ratio	0V ≤ V_{CM} ≤ 4V	50	65		dB
PSRR	Power Supply Rejection Ratio	2.7V ≤ V^+ ≤ 5V V_O = 1V, V_{CM} = 1V	50	60		dB
V_{CM}	Input Common-Mode Voltage Range	For CMRR ≥ 50 dB	0	−0.2		V
				4.2	4	V
A_V	Large Signal Voltage Gain (3)	R_L = 2 kΩ	15 **10**	100		V/mV
V_O	Output Swing	R_L = 2 kΩ to 2.5V	V^+ − 300 **V^+ − 400**	V^+ −40		mV
		R_L = 2 kΩ to 2.5V		120	300 **400**	
		R_L = 10 kΩ to 2.5V	V^+ − 100 **V^+ − 200**	V^+ − 10		mV
		R_L = 2 kΩ to 2.5V, 125°C		65	180 **280**	
I_O	Output Short Circuit Current	Sourcing, V_O = 0V	5	60		mA
		Sinking, V_O = 5V	10	160		
I_S	Supply Current	LMV321-N		130	250 **350**	µA
		LMV358-N (both amps)		210	440 **615**	
		LMV324-N (all four amps)		410	830 **1160**	

(1) All limits are guaranteed by testing or statistical analysis.
(2) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not guaranteed on shipped production material.
(3) R_L is connected to V^-. The output voltage is 0.5V ≤ V_O ≤ 4.5V.

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5V AC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for T_J = 25°C, V^+ = 5V, V^- = 0V, V_{CM} = 2.0V, V_O = V^+/2 and R_L > 1 MΩ. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (1)	Typ (2)	Max (1)	Units
SR	Slew Rate	(3)		1		V/µs
GBWP	Gain-Bandwidth Product	C_L = 200 pF		1		MHz
Φ_m	Phase Margin			60		Deg
G_m	Gain Margin			10		dB
e_n	Input-Referred Voltage Noise	f = 1 kHz		39		$\frac{nV}{\sqrt{Hz}}$
i_n	Input-Referred Current Noise	f = 1 kHz		0.21		$\frac{pA}{\sqrt{Hz}}$

(1) All limits are guaranteed by testing or statistical analysis.
(2) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not guaranteed on shipped production material.
(3) Connected as voltage follower with 3V step input. Number specified is the slower of the positive and negative slew rates.

CONNECTION DIAGRAM

5-Pin SC70/SOT23

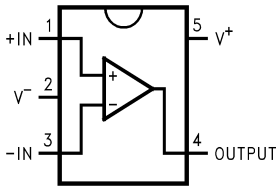

Figure 1. Top View

8-Pin SOIC/MSOP

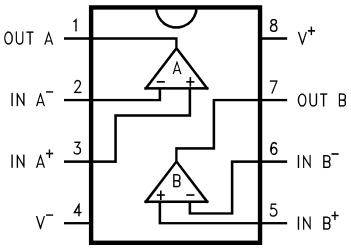

Figure 2. Top View

14-Pin SOIC/TSSOP

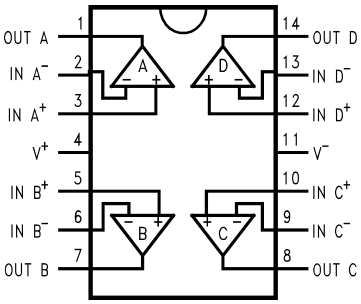

Figure 3. Top View

Devices with an asterisk (*) are future products. Please contact the factory for availability.

Automotive Grade (Q) product incorporates enhanced manufacturing and support processes for the automotive market, includingdefect detection methodologies. Reliability qualification is compliant with the requirements and temperature grades defined in the AEC Q100 standard. Automotive Grade products are identified with the letter Q. Fully compliant PPAP documentation is available.For more information go to http://www.national.com/automotive.

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Typical Performance Characteristics

Unless otherwise specified, V_S = +5V, single supply, T_A = 25°C.

Supply Current vs. Supply Voltage (LMV321-N)

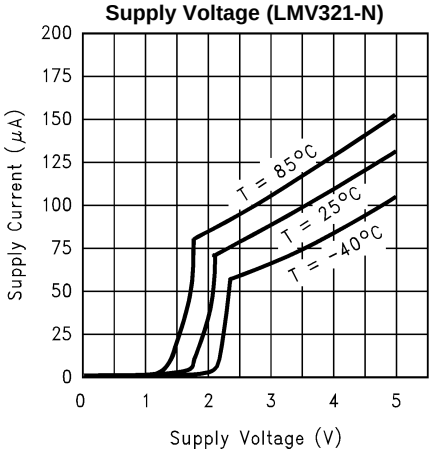

Figure 4.

Input Current vs. Temperature

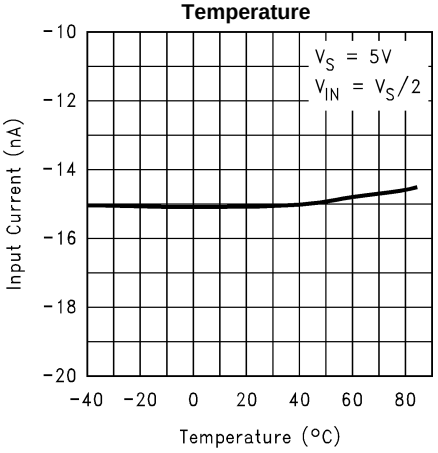

Figure 5.

Sourcing Current vs. Output Voltage

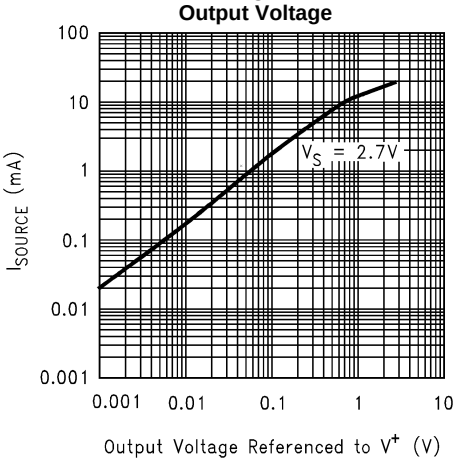

Figure 6.

Sourcing Current vs. Output Voltage

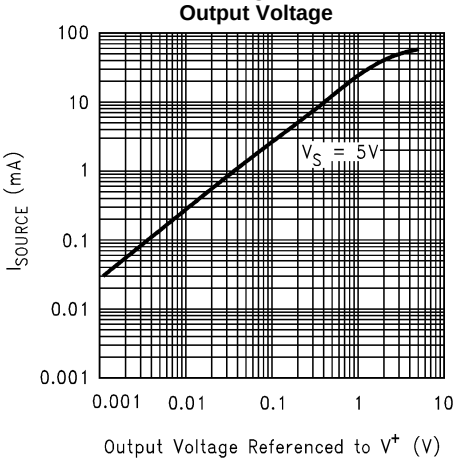

Figure 7.

Sinking Current vs. Output Voltage

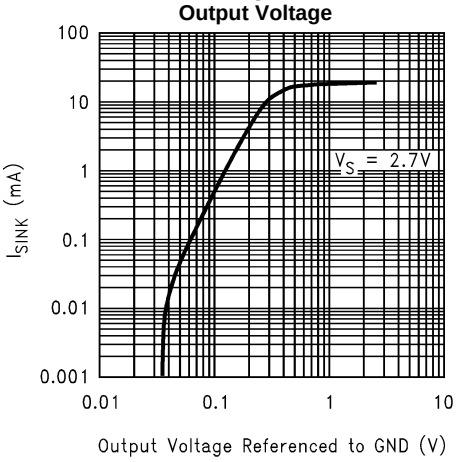

Figure 8.

Sinking Current vs. Output Voltage

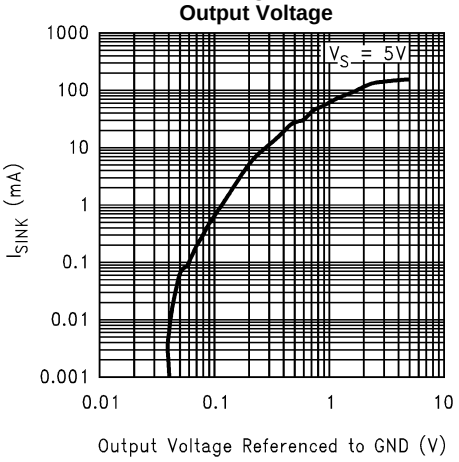

Figure 9.

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Typical Performance Characteristics (continued)

Unless otherwise specified, V_S = +5V, single supply, T_A = 25°C.

Output Voltage Swing vs. Supply Voltage

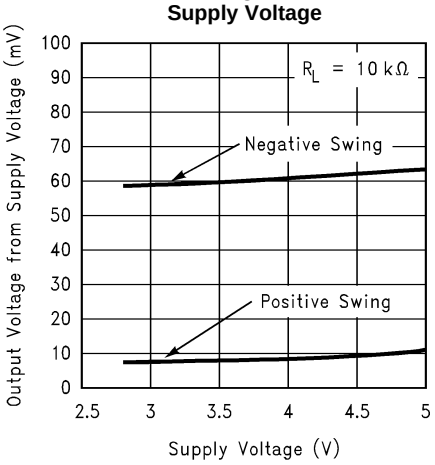

Figure 10.

Input Voltage Noise vs. Frequency

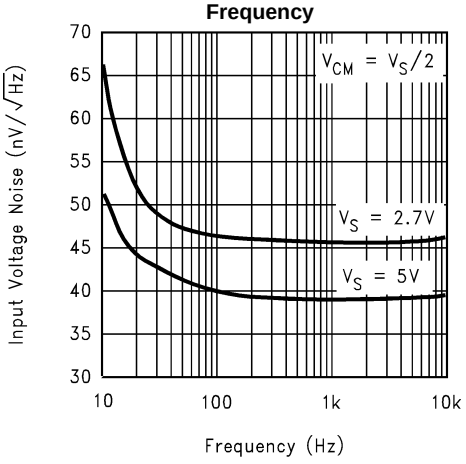

Figure 11.

Input Current Noise vs. Frequency

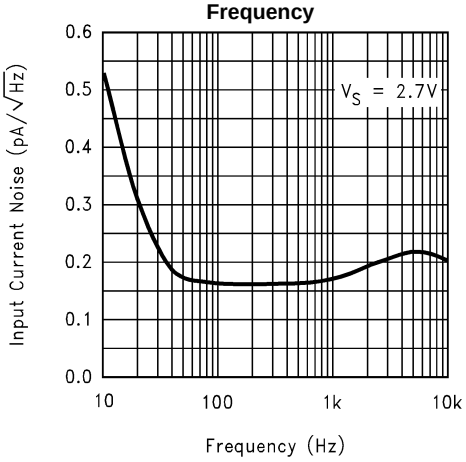

Figure 12.

Input Current Noise vs. Frequency

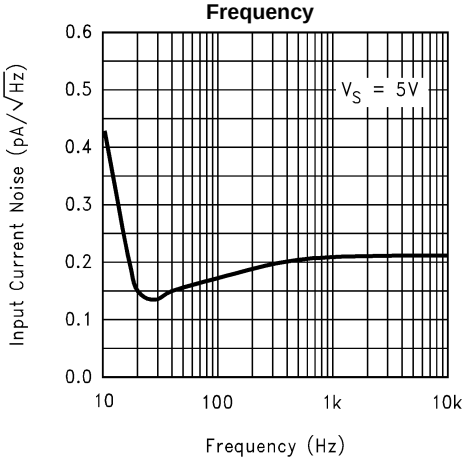

Figure 13.

Crosstalk Rejection vs. Frequency

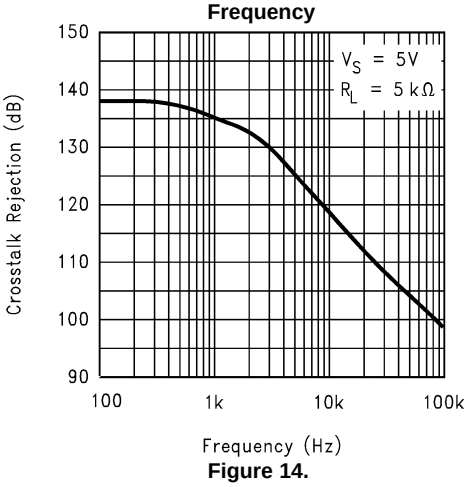

Figure 14.

PSRR vs. Frequency

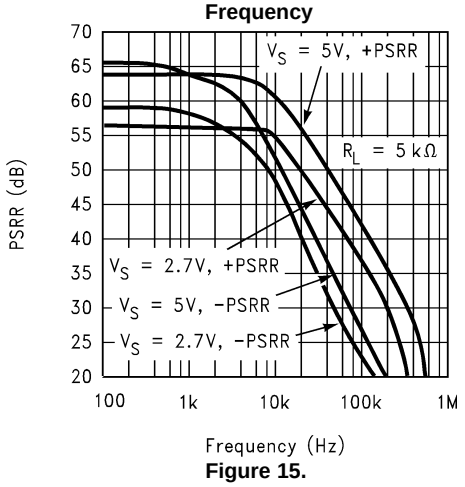

Figure 15.

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Typical Performance Characteristics (continued)

Unless otherwise specified, V_S = +5V, single supply, T_A = 25°C.

CMRR vs. Frequency

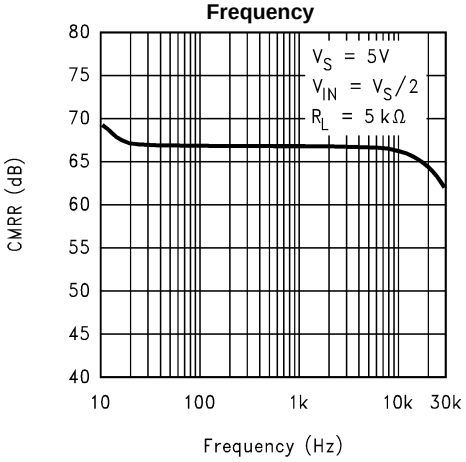

Figure 16.

CMRR vs. Input Common Mode Voltage

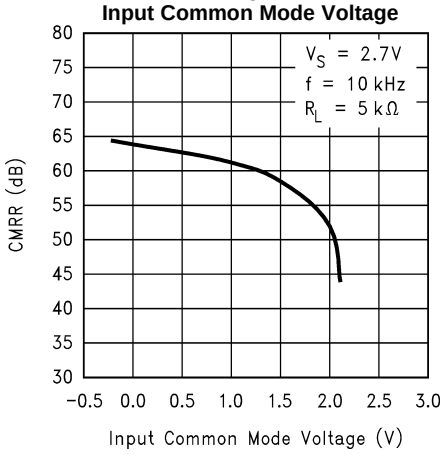

Figure 17.

CMRR vs. Input Common Mode Voltage

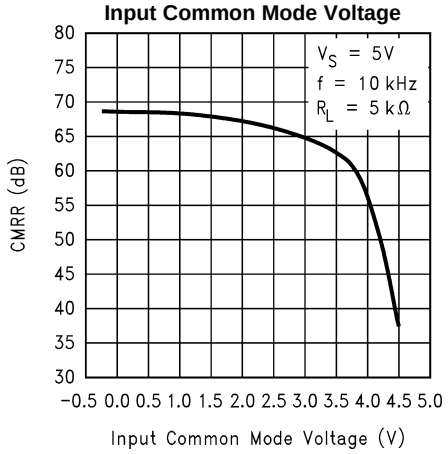

Figure 18.

ΔV_{OS} vs. CMR

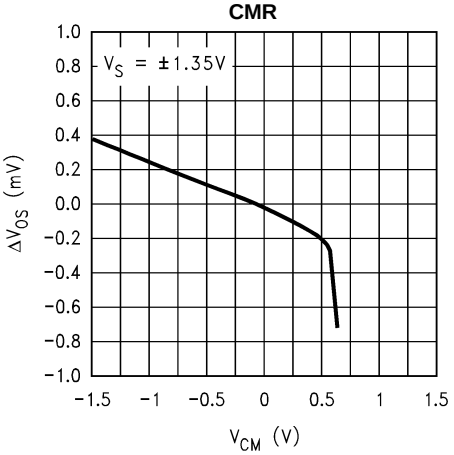

Figure 19.

ΔV_{OS} vs. CMR

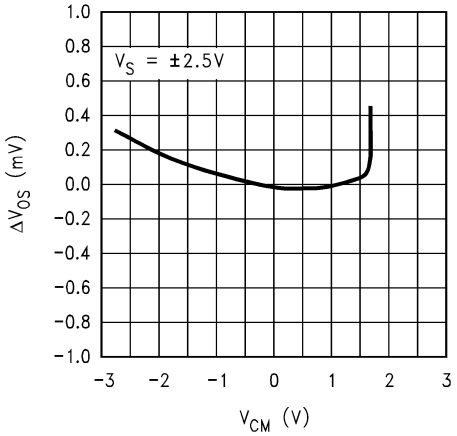

Figure 20.

Input Voltage vs. Output Voltage

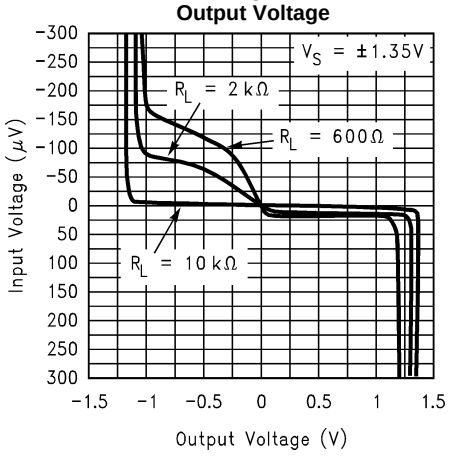

Figure 21.

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Typical Performance Characteristics (continued)

Unless otherwise specified, V_S = +5V, single supply, T_A = 25°C.

Input Voltage vs. Output Voltage

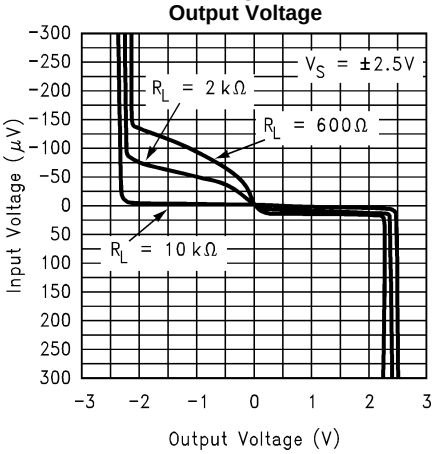

Figure 22.

Open Loop Frequency Response

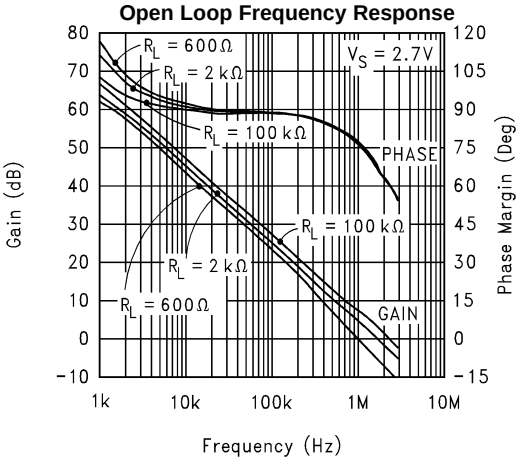

Figure 23.

Open Loop Frequency Response

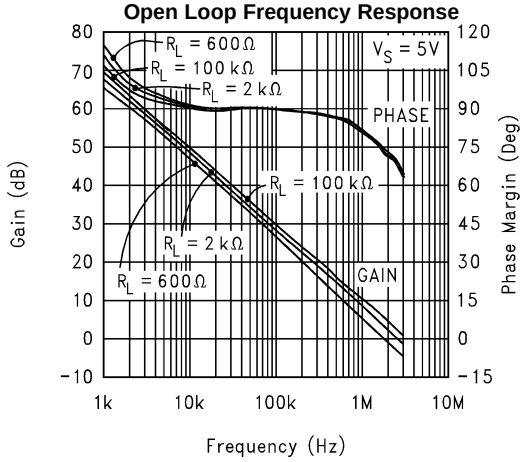

Figure 24.

Open Loop Frequency Response vs. Temperature

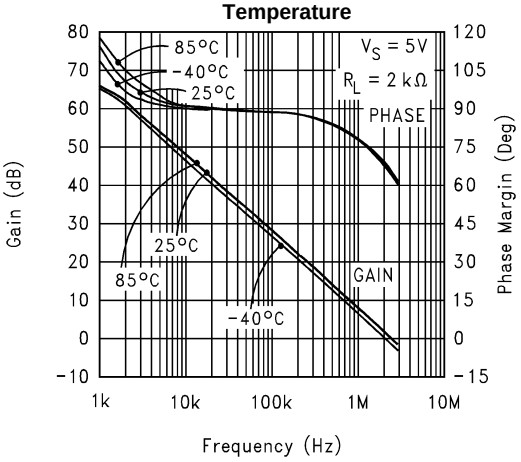

Figure 25.

Gain and Phase vs. Capacitive Load

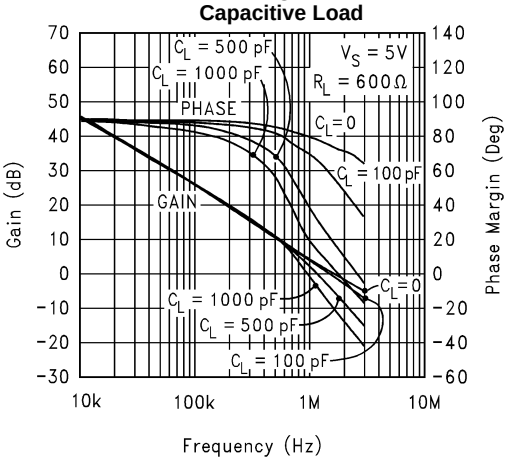

Figure 26.

Gain and Phase vs. Capacitive Load

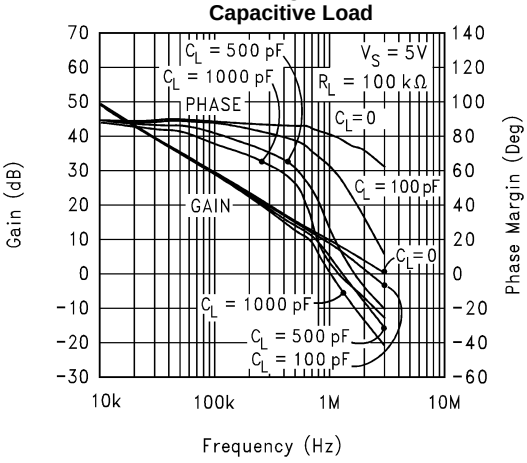

Figure 27.

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Typical Performance Characteristics (continued)

Unless otherwise specified, V_S = +5V, single supply, T_A = 25°C.

Slew Rate vs. Supply Voltage

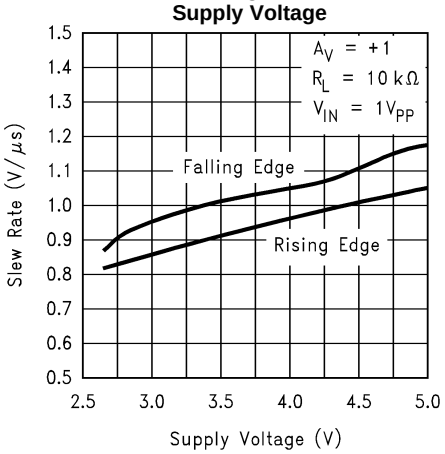

Figure 28.

Non-Inverting Large Signal Pulse Response

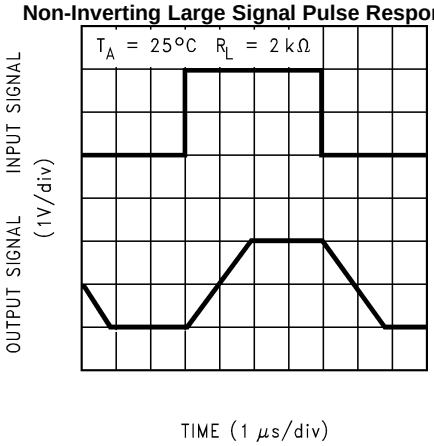

Figure 29.

Non-Inverting Large Signal Pulse Response

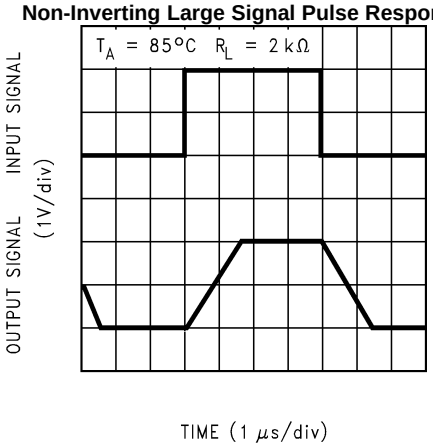

Figure 30.

Non-Inverting Large Signal Pulse Response

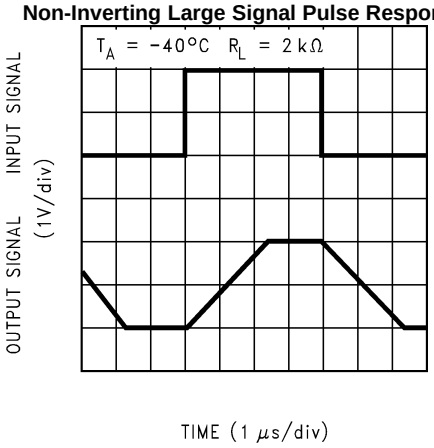

Figure 31.

Non-Inverting Small Signal Pulse Response

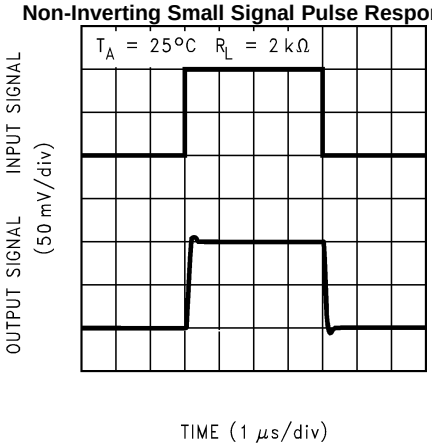

Figure 32.

Non-Inverting Small Signal Pulse Response

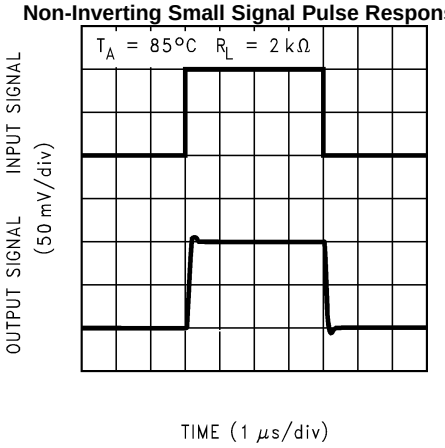

Figure 33.

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Typical Performance Characteristics (continued)

Unless otherwise specified, V_S = +5V, single supply, T_A = 25°C.

Non-Inverting Small Signal Pulse Response

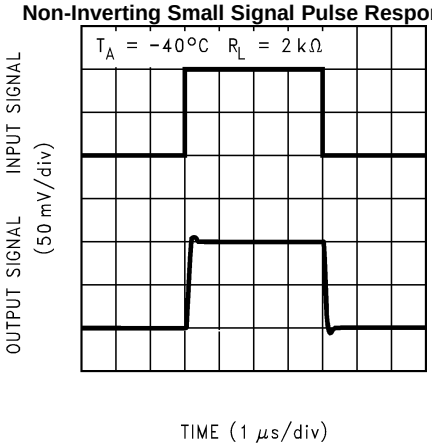

Figure 34.

Inverting Large Signal Pulse Response

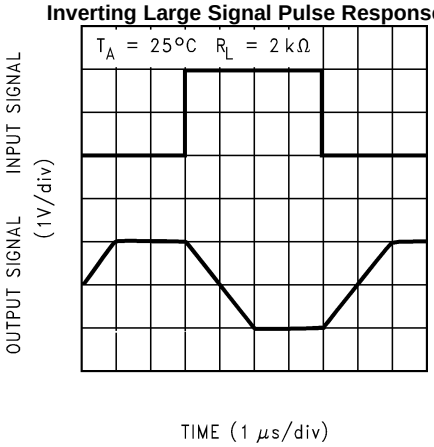

Figure 35.

Inverting Large Signal Pulse Response

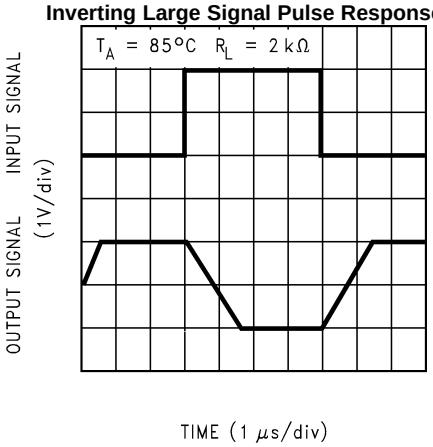

Figure 36.

Inverting Large Signal Pulse Response

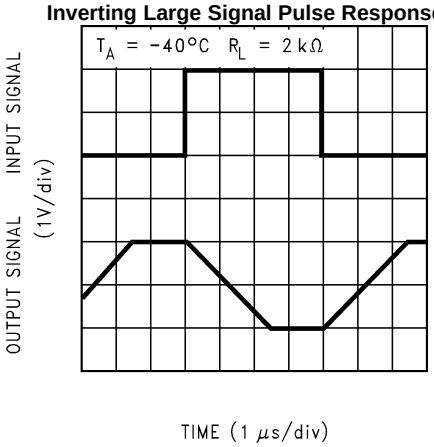

Figure 37.

Inverting Small Signal Pulse Response

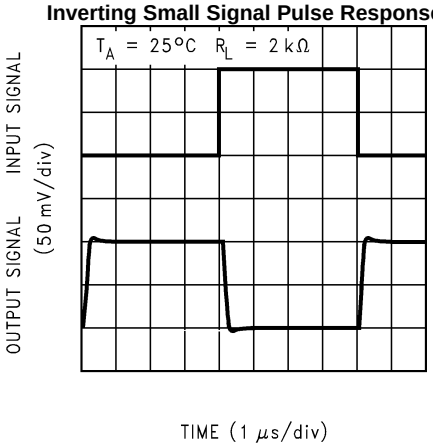

Figure 38.

Inverting Small Signal Pulse Response

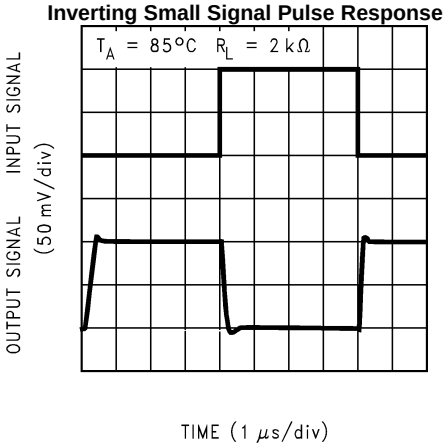

Figure 39.

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Typical Performance Characteristics (continued)

Unless otherwise specified, V_S = +5V, single supply, T_A = 25°C.

Inverting Small Signal Pulse Response

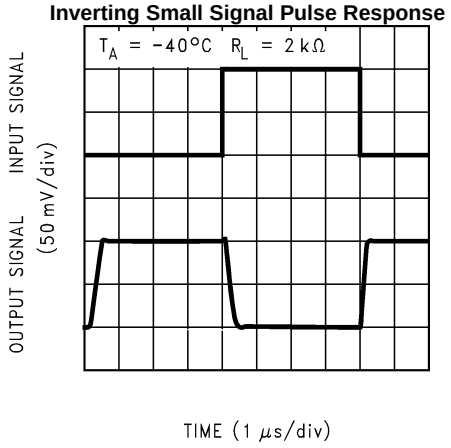

Figure 40.

Stability vs. Capacitive Load

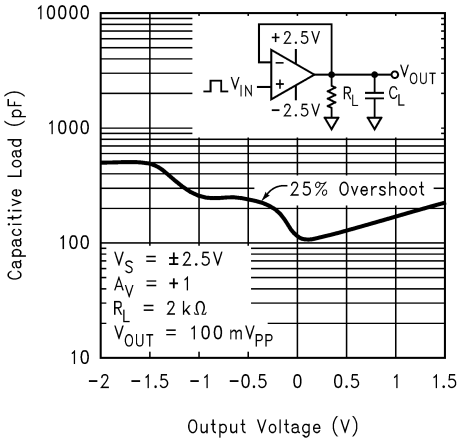

Figure 41.

Stability vs. Capacitive Load

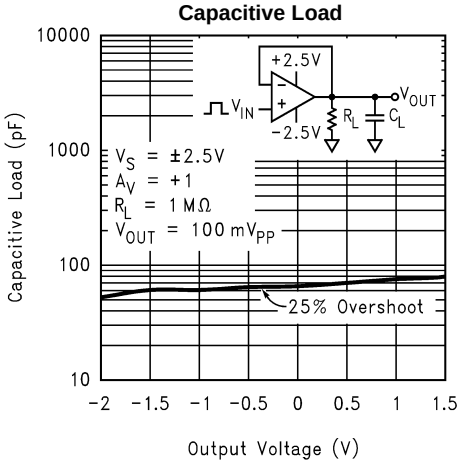

Figure 42.

Stability vs. Capacitive Load

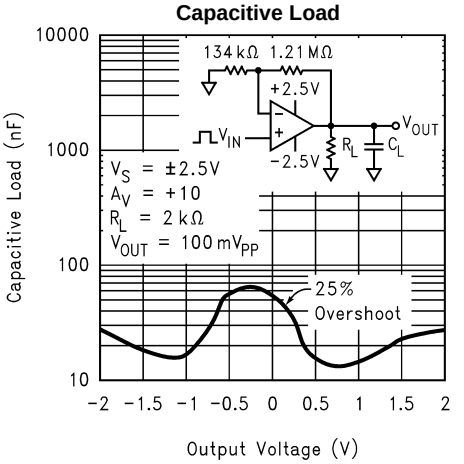

Figure 43.

Stability vs. Capacitive Load

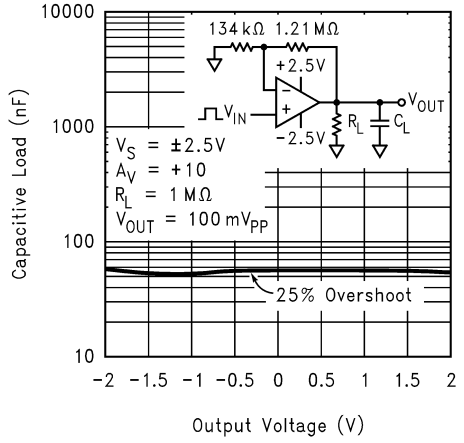

Figure 44.

THD vs. Frequency

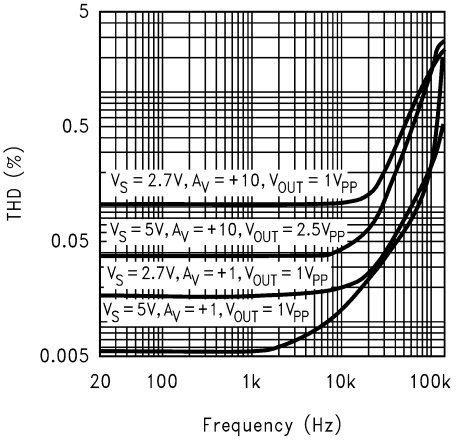

Figure 45.

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Typical Performance Characteristics (continued)

Unless otherwise specified, V_S = +5V, single supply, T_A = 25°C.

Open Loop Output Impedance vs. Frequency

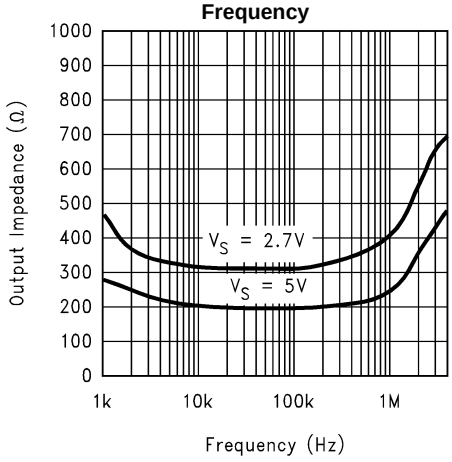

Figure 46.

Short Circuit Current vs. Temperature (Sinking)

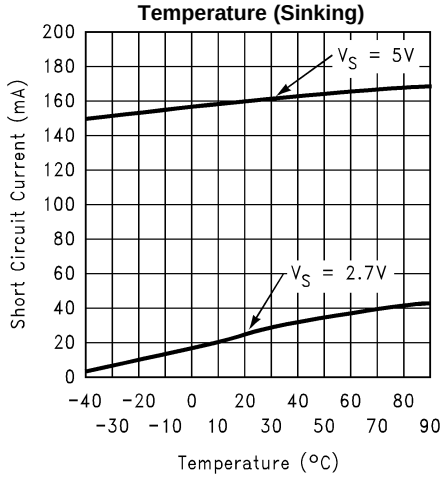

Figure 47.

Short Circuit Current vs. Temperature (Sourcing)

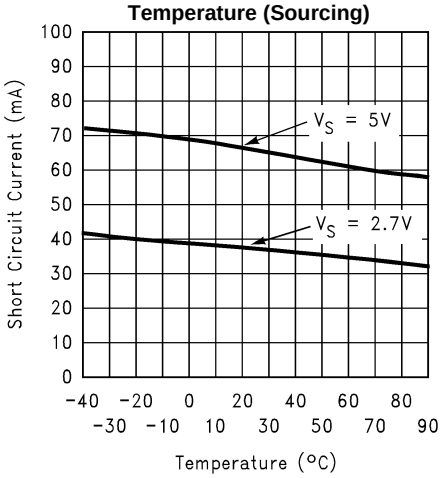

Figure 48.

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APPLICATION INFORMATION

BENEFITS OF THE LMV321-N/LMV358-N/LMV324-N

Size

The small footprints of the LMV321-N/LMV358-N/LMV324-N packages save space on printed circuit boards, and enable the design of smaller electronic products, such as cellular phones, pagers, or other portable systems. The low profile of the LMV321-N/LMV358-N/LMV324-N make them possible to use in PCMCIA type III cards.

Signal Integrity

Signals can pick up noise between the signal source and the amplifier. By using a physically smaller amplifier package, the LMV321-N/LMV358-N/LMV324-N can be placed closer to the signal source, reducing noise pickup and increasing signal integrity.

Simplified Board Layout

These products help you to avoid using long PC traces in your PC board layout. This means that no additional components, such as capacitors and resistors, are needed to filter out the unwanted signals due to the interference between the long PC traces.

Low Supply Current

These devices will help you to maximize battery life. They are ideal for battery powered systems.

Low Supply Voltage

Texas Instruments provides guaranteed performance at 2.7V and 5V. These guarantees ensure operation throughout the battery lifetime.

Rail-to-Rail Output

Rail-to-rail output swing provides maximum possible dynamic range at the output. This is particularly important when operating on low supply voltages.

Input Includes Ground

Allows direct sensing near GND in single supply operation.

Protection should be provided to prevent the input voltages from going negative more than −0.3V (at 25°C). An input clamp diode with a resistor to the IC input terminal can be used.

Ease of Use and Crossover Distortion

The LMV321-N/LMV358-N/LMV324-N offer specifications similar to the familiar LM324-N. In addition, the new LMV321-N/LMV358-N/LMV324-N effectively eliminate the output crossover distortion. The scope photos in Figure 49 and Figure 50 compare the output swing of the LMV324-N and the LM324-N in a voltage follower configuration, with V_S = ± 2.5V and R_L (= 2 kΩ) connected to GND. It is apparent that the crossover distortion has been eliminated in the new LMV324-N.

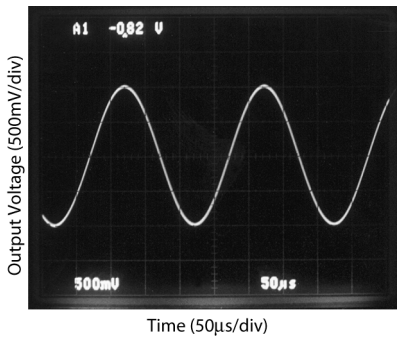

Figure 49. Output Swing of LMV324

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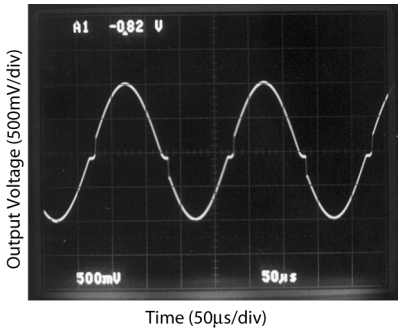

Figure 50. Output Swing of LM324

CAPACITIVE LOAD TOLERANCE

The LMV321-N/LMV358-N/LMV324-N can directly drive 200 pF in unity-gain without oscillation. The unity-gain follower is the most sensitive configuration to capacitive loading. Direct capacitive loading reduces the phase margin of amplifiers. The combination of the amplifier's output impedance and the capacitive load induces phase lag. This results in either an underdamped pulse response or oscillation. To drive a heavier capacitive load, the circuit in Figure 51 can be used.

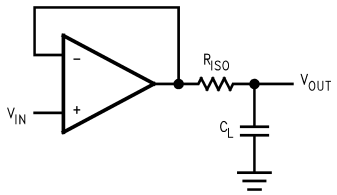

Figure 51. Indirectly Driving a Capacitive Load Using Resistive Isolation

In Figure 51 , the isolation resistor R_{ISO} and the load capacitor C_L form a pole to increase stability by adding more phase margin to the overall system. The desired performance depends on the value of R_{ISO}. The bigger the R_{ISO} resistor value, the more stable V_{OUT} will be. Figure 52 is an output waveform of Figure 51 using 620Ω for R_{ISO} and 510 pF for C_L.

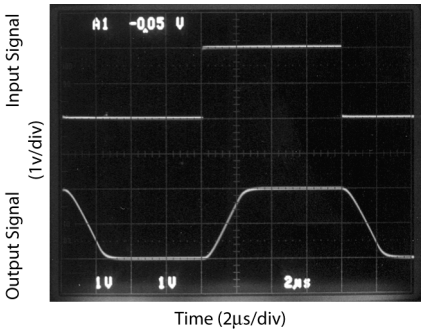

Figure 52. Pulse Response of the LMV324 Circuit in Figure 51

The circuit in Figure 53 is an improvement to the one in Figure 51 because it provides DC accuracy as well as AC stability. If there were a load resistor in Figure 51, the output would be voltage divided by R_{ISO} and the load resistor. Instead, in Figure 53, R_F provides the DC accuracy by using feed-forward techniques to connect V_{IN} to R_L. Caution is needed in choosing the value of R_F due to the input bias current of theLMV321-N/LMV358-N/LMV324-N. C_F and R_{ISO} serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving phase margin in the overall feedback loop. Increased capacitive drive is possible by increasing the value of C_F . This in turn will slow down the pulse response.

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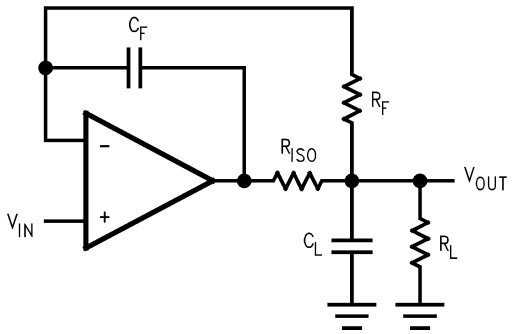

Figure 53. Indirectly Driving A Capacitive Load with DC Accuracy

INPUT BIAS CURRENT CANCELLATION

The LMV321-N/LMV358-N/LMV324-N family has a bipolar input stage. The typical input bias current of LMV321-N/LMV358-N/LMV324-N is 15 nA with 5V supply. Thus a 100 kΩ input resistor will cause 1.5 mV of error voltage. By balancing the resistor values at both inverting and non-inverting inputs, the error caused by the amplifier's input bias current will be reduced. The circuit in Figure 54 shows how to cancel the error caused by input bias current.

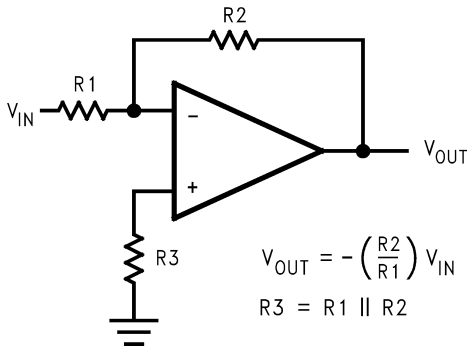

Figure 54. Cancelling the Error Caused by Input Bias Current

TYPICAL SINGLE-SUPPLY APPLICATION CIRCUITS

Difference Amplifier

The difference amplifier allows the subtraction of two voltages or, as a special case, the cancellation of a signal common to two inputs. It is useful as a computational amplifier, in making a differential to single-ended conversion or in rejecting a common mode signal.

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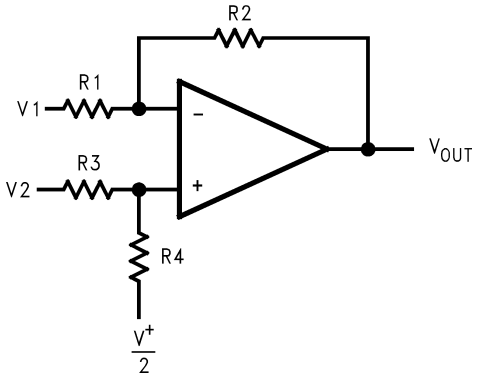

$$V_{OUT} = \left(\frac{R1 + R2}{R3 + R4}\right)\frac{R4}{R1}V_2 - \frac{R2}{R1}V_1 + \left(\frac{R1 + R2}{R3 + R4}\right)\frac{R3}{R1} \bullet \frac{V^+}{2}$$

for R1 = R3 and R2 = R4

$$V_{OUT} = \frac{R2}{R1}(V_2 - V_1) + \frac{V^+}{2}$$

Figure 55. Difference Amplifier

Instrumentation Circuits

The input impedance of the previous difference amplifier is set by the resistors R_1, R_2, R_3, and R_4. To eliminate the problems of low input impedance, one way is to use a voltage follower ahead of each input as shown in the following two instrumentation amplifiers.

Three-Op-Amp Instrumentation Amplifier

The quad LMV324 can be used to build a three-op-amp instrumentation amplifier as shown in Figure 56.

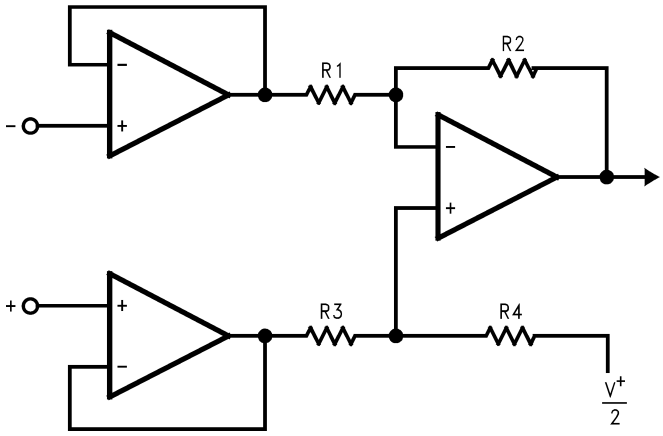

Figure 56. Three-Op-Amp Instrumentation Amplifier

The first stage of this instrumentation amplifier is a differential-input, differential-output amplifier, with two voltage followers. These two voltage followers assure that the input impedance is over 100 MΩ. The gain of this instrumentation amplifier is set by the ratio of R_2/R_1. R_3 should equal R_1, and R_4 equal R_2. Matching of R_3 to R_1 and R_4 to R_2 affects the CMRR. For good CMRR over temperature, low drift resistors should be used. Making R_4 slightly smaller than R_2 and adding a trim pot equal to twice the difference between R_2 and R_4 will allow the CMRR to be adjusted for optimum performance.

Two-Op-Amp Instrumentation Amplifier

A two-op-amp instrumentation amplifier can also be used to make a high-input-impedance DC differential amplifier (Figure 57). As in the three-op-amp circuit, this instrumentation amplifier requires precise resistor matching for good CMRR. R_4 should equal R_1 and, R_3 should equal R_2.

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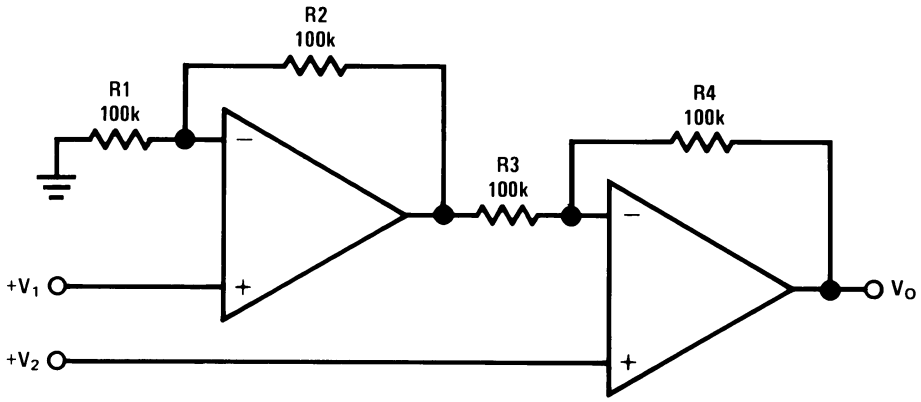


$$V_O = \left(1 + \frac{R4}{R3}\right)(V_2 - V_1), \text{ where } R1 = R4 \text{ and } R2 = R3$$

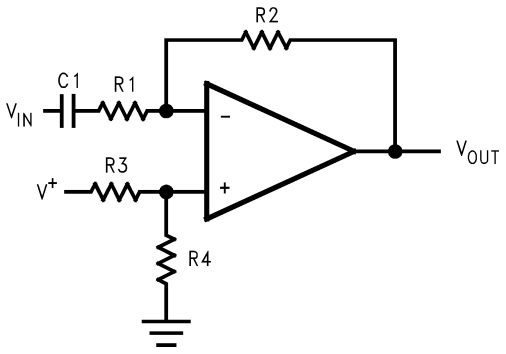
$$\text{As shown: } V_O = 2(V_2 - V_1)$$

Figure 57. Two-Op-Amp Instrumentation Amplifier

Single-Supply Inverting Amplifier

There may be cases where the input signal going into the amplifier is negative. Because the amplifier is operating in single supply voltage, a voltage divider using R_3 and R_4 is implemented to bias the amplifier so the input signal is within the input common-mode voltage range of the amplifier. The capacitor C_1 is placed between the inverting input and resistor R_1 to block the DC signal going into the AC signal source, V_{IN}. The values of R_1 and C_1 affect the cutoff frequency, fc = $1/2\pi R_1 C_1$.

As a result, the output signal is centered around mid-supply (if the voltage divider provides $V^+/2$ at the non-inverting input). The output can swing to both rails, maximizing the signal-to-noise ratio in a low voltage system.



$$V_{OUT} = -\frac{R2}{R1} V_{IN}$$

Figure 58. Single-Supply Inverting Amplifier

ACTIVE FILTER

Simple Low-Pass Active Filter

The simple low-pass filter is shown in Figure 59. Its low-frequency gain ($\omega \rightarrow 0$) is defined by $-R_3/R_1$. This allows low-frequency gains other than unity to be obtained. The filter has a −20 dB/decade roll-off after its corner frequency fc. R_2 should be chosen equal to the parallel combination of R_1 and R_3 to minimize errors due to bias current. The frequency response of the filter is shown in Figure 60.

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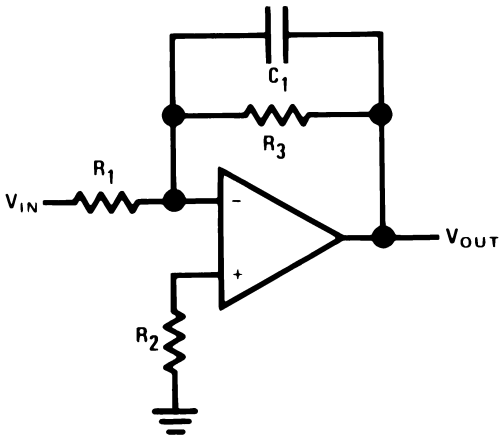

$$A_L = -\frac{R_3}{R_1}$$

$$f_c = \frac{1}{2\pi R_3 C_1}$$

$$R_2 = R_1 \parallel R_3$$

Figure 59. Simple Low-Pass Active Filter

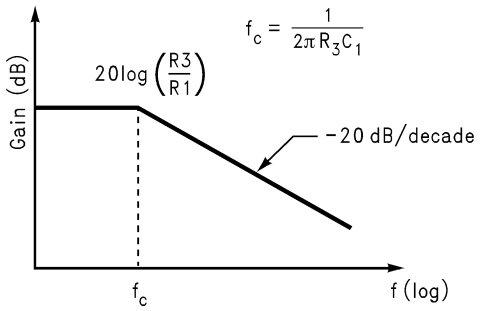

Figure 60. Frequency Response of Simple Low-Pass Active Filter in Figure 11

Note that the single-op-amp active filters are used in the applications that require low quality factor, Q(≤ 10), low frequency (≤ 5 kHz), and low gain (≤ 10), or a small value for the product of gain times Q (≤ 100). The op amp should have an open loop voltage gain at the highest frequency of interest at least 50 times larger than the gain of the filter at this frequency. In addition, the selected op amp should have a slew rate that meets the following requirement:

$$\text{Slew Rate} \geq 0.5 \times (\omega_H V_{OPP}) \times 10^{-6}\ \text{V/µsec} \quad (1)$$

where ω_H is the highest frequency of interest, and V_{OPP} is the output peak-to-peak voltage.

Sallen-Key 2nd-Order Active Low-Pass Filter

The Sallen-Key 2nd-order active low-pass filter is illustrated in Figure 61. The DC gain of the filter is expressed as

$$A_{LP} = \frac{R_3}{R_4} + 1 \quad (2)$$

Its transfer function is

$$\frac{V_{OUT}}{V_{IN}}(S) = \frac{\frac{1}{C_1 C_2 R_1 R_2} A_{LP}}{S^2 + S\left(\frac{1}{C_1 R_1} + \frac{1}{C_1 R_2} + \frac{1}{C_2 R_2} - \frac{A_{LP}}{C_2 R_2}\right) + \frac{1}{C_1 C_2 R_1 R_2}} \quad (3)$$

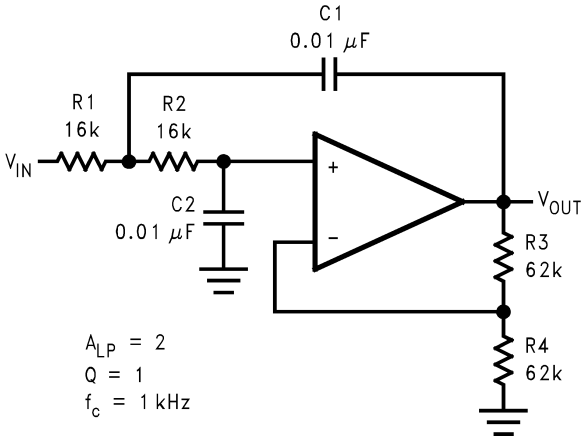

Figure 61. Sallen-Key 2nd-Order Active Low-Pass Filter

The following paragraphs explain how to select values for R_1, R_2, R_3, R_4, C_1, and C_2 for given filter requirements, such as A_{LP}, Q, and f_c.

The standard form for a 2nd-order low pass filter is

$$\frac{V_{OUT}}{V_{IN}}(S) = \frac{A_{LP}\,\omega_c^2}{S^2 + \left(\frac{\omega_c}{Q}\right)S + \omega_c^2} \quad (4)$$

where

Q: Pole Quality Factor

ω_C: Corner Frequency

A comparison between Equation 3 and Equation 4 yields

$$\omega_c^2 = \frac{1}{C_1 C_2 R_1 R_2} \quad (5)$$

$$\frac{\omega_c}{Q} = \frac{1}{C_1 R_1} + \frac{1}{C_1 R_2} + \frac{1}{C_2 R_2} - \frac{A_{LP}}{C_2 R_2} \quad (6)$$

To reduce the required calculations in filter design, it is convenient to introduce normalization into the components and design parameters. To normalize, let $\omega_C = \omega_n = 1$ rad/s, and $C_1 = C_2 = C_n = 1$F, and substitute these values into Equation 5 and Equation 6. From Equation 5, we obtain

$$R_1 = \frac{1}{R_2} \quad (7)$$

From Equation 6, we obtain

$$R_2 = \frac{1 \pm \sqrt{1 - 4Q^2(2 - A_{LP})}}{2Q} \quad (8)$$

For minimum DC offset, $V^+ = V^-$, the resistor values at both inverting and non-inverting inputs should be equal, which means

$$R_1 + R_2 = \frac{R_3 R_4}{R_3 + R_4} \quad (9)$$

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From Equation 2 and Equation 9, we obtain

$$R_3 = (R_1 + R_2)A_{LP} \quad (10)$$

$$R_4 = \left(\frac{A_{LP}}{A_{LP}-1}\right)(R_1 + R_2) \quad (11)$$

The values of C_1 and C_2 are normally close to or equal to

$$C = \frac{10}{f_c}\,\mu F \quad (12)$$

As a design example:

Require: A_{LP} = 2, Q = 1, fc = 1 kHz

Start by selecting C_1 and C_2. Choose a standard value that is close to

$$C = \frac{10}{f_c}\,\mu F \quad (13)$$

$$C_1 = C_2 = \frac{10}{1 \times 10^3}\,\mu F = 0.01\,\mu F \quad (14)$$

From Equation 7 Equation 8 Equation 10 Equation 11,

R_1= 1Ω (15)

R_2= 1Ω (16)

R_3= 4Ω (17)

R_4= 4Ω (18)

The above resistor values are normalized values with ω_n = 1 rad/s and $C_1 = C_2 = C_n$ = 1F. To scale the normalized cutoff frequency and resistances to the real values, two scaling factors are introduced, frequency scaling factor (k_f) and impedance scaling factor (k_m).

$$k_f = \frac{\omega_c}{\omega_n} = \frac{2\pi \times 1 \times 10^3}{1} = 2\pi \times 10^3$$

$$k_m k_f = \frac{Cn}{C1}$$

$$k_m = 1.59 \times 10^4 \quad (19)$$

Scaled values:

$R_2 = R_1$ = 15.9 kΩ (20)

$R_3 = R_4$ = 63.6 kΩ (21)

$C_1 = C_2$ = 0.01 µF (22)

An adjustment to the scaling may be made in order to have realistic values for resistors and capacitors. The actual value used for each component is shown in the circuit.

2nd-Order High Pass Filter

A 2nd-order high pass filter can be built by simply interchanging those frequency selective components (R_1, R_2, C_1, C_2) in the Sallen-Key 2nd-order active low pass filter. As shown in Figure 62, resistors become capacitors, and capacitors become resistors. The resulted high pass filter has the same corner frequency and the same maximum gain as the previous 2nd-order low pass filter if the same components are chosen.

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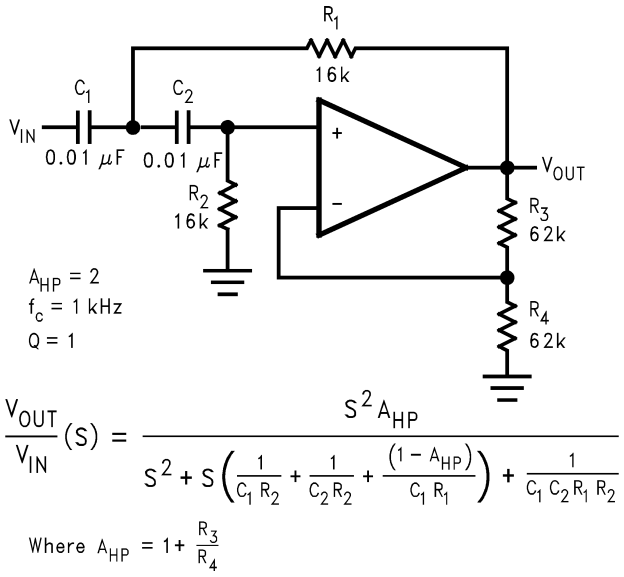

Figure 62. Sallen-Key 2nd-Order Active High-Pass Filter

State Variable Filter

A state variable filter requires three op amps. One convenient way to build state variable filters is with a quad op amp, such as the LMV324 (Figure 63).

This circuit can simultaneously represent a low-pass filter, high-pass filter, and bandpass filter at three different outputs. The equations for these functions are listed below. It is also called "Bi-Quad" active filter as it can produce a transfer function which is quadratic in both numerator and denominator.

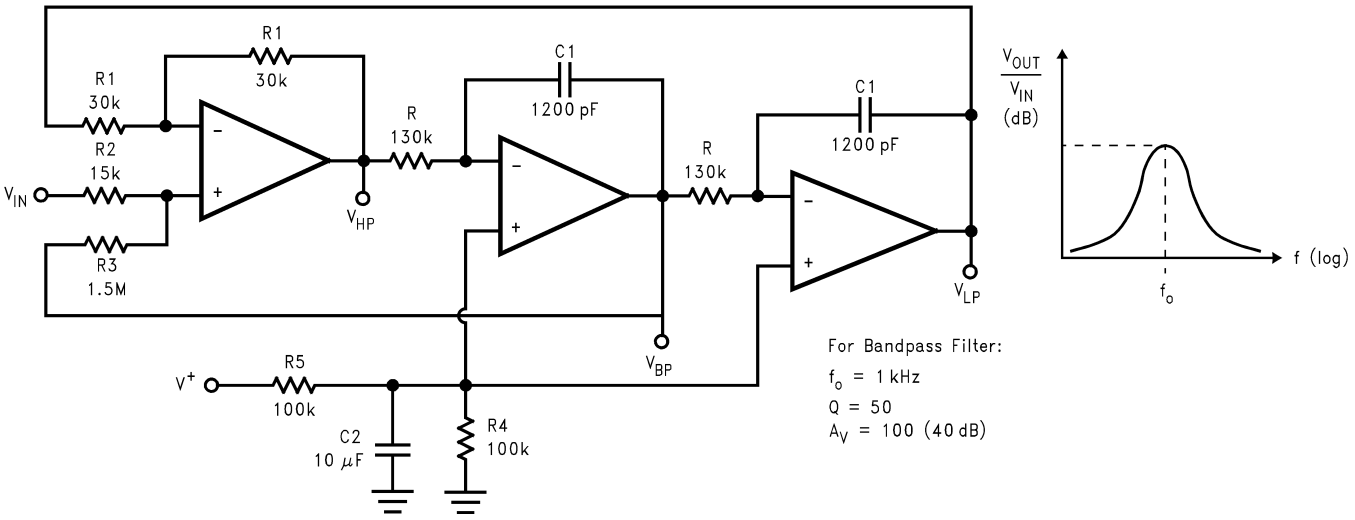

Figure 63. State Variable Active Filter

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$$V_{LP} = \left(\frac{2R_3}{R_2 + R_3}\right) \frac{\frac{1}{R^2C^2}}{S^2 + \frac{1}{\left(\frac{R_2 + R_3}{2R_2}\right)RC} S + \frac{1}{R^2C^2}} V_{IN}$$

$$V_{HP} = \left(\frac{2R_3}{R_2 + R_3}\right) \frac{S^2}{S^2 + \frac{1}{\left(\frac{R_2 + R_3}{2R_2}\right)RC} S + \frac{1}{R^2C^2}} V_{IN}$$

$$V_{BP} = \left(\frac{2R_3}{R_2 + R_3}\right) \frac{\left(\frac{1}{RC}\right)S}{S^2 + \frac{1}{\left(\frac{R_2 + R_3}{2R_2}\right)RC} S + \frac{1}{R^2C^2}} V_{IN} \quad (23)$$

where for all three filters,

$$Q = \frac{R_2 + R_3}{2R_2} \quad (24)$$

$$\omega_0 = \frac{1}{RC} \quad \text{(resonant frequency)} \quad (25)$$

A design example for a bandpass filter is shown below:

Assume the system design requires a bandpass filter with f_O = 1 kHz and Q = 50. What needs to be calculated are capacitor and resistor values.

First choose convenient values for C_1, R_1 and R_2:

C_1 = 1200 pF (26)

$2R_2 = R_1$ = 30 kΩ (27)

Then from Equation 24,

$$R_3 = R_2(2Q-1)$$

$$R_3 = 15\ k\Omega \times (2 \times 50 - 1)$$

$$= 1.5\ M\Omega \quad (28)$$

From Equation 25,

$$R = \frac{1}{\omega_0 C_1}$$

$$R = \frac{1}{(2\pi \times 10^3)(1.2 \times 10^{-9})}$$

$$= 132.7\ k\Omega \quad (29)$$

From the above calculated values, the midband gain is $H_0 = R_3/R_2$ = 100 (40 dB). The nearest 5% standard values have been added to Figure 63.

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PULSE GENERATORS AND OSCILLATORS

A pulse generator is shown in Figure 64. Two diodes have been used to separate the charge and discharge paths to capacitor C.

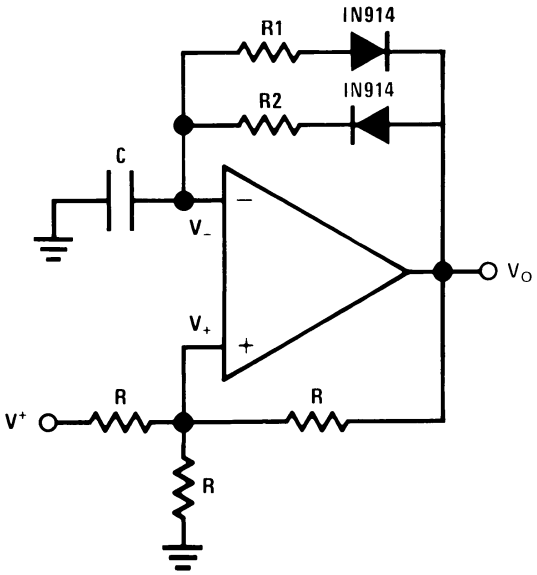

Figure 64. Pulse Generator

When the output voltage V_O is first at its high, V_{OH}, the capacitor C is charged toward V_{OH} through R_2. The voltage across C rises exponentially with a time constant $\tau = R_2C$, and this voltage is applied to the inverting input of the op amp. Meanwhile, the voltage at the non-inverting input is set at the positive threshold voltage (V_{TH+}) of the generator. The capacitor voltage continually increases until it reaches V_{TH+}, at which point the output of the generator will switch to its low, V_{OL} which 0V is in this case. The voltage at the non-inverting input is switched to the negative threshold voltage (V_{TH-}) of the generator. The capacitor then starts to discharge toward V_{OL} exponentially through R_1, with a time constant $\tau = R_1C$. When the capacitor voltage reaches V_{TH-}, the output of the pulse generator switches to V_{OH}. The capacitor starts to charge, and the cycle repeats itself.

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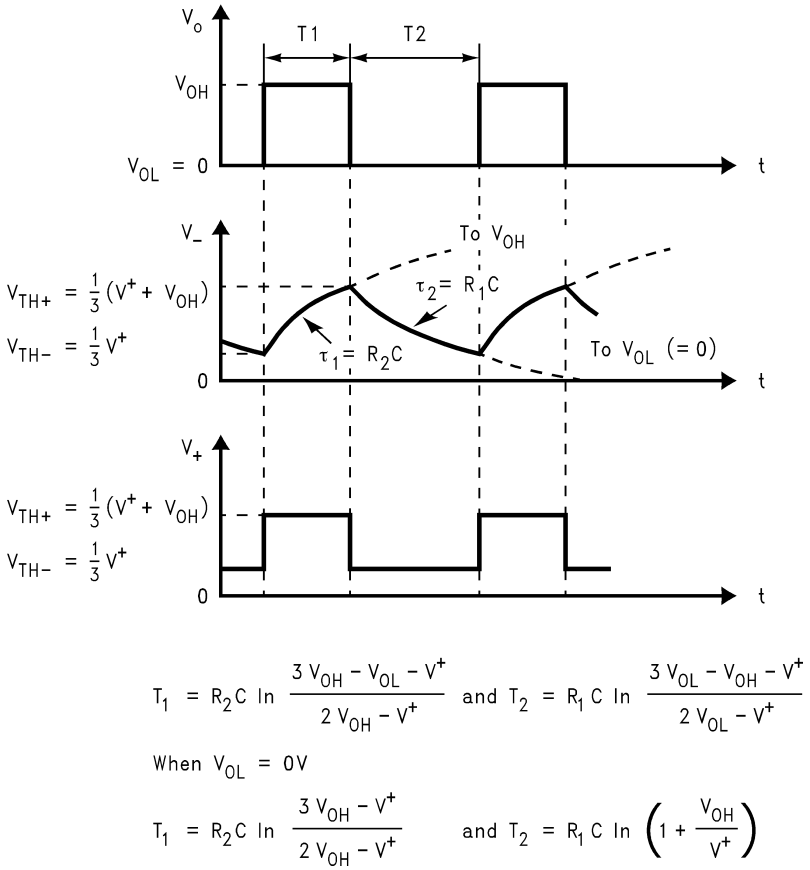

Figure 65. Waveforms of the Circuit in Figure 16

As shown in the waveforms in Figure 65, the pulse width (T_1) is set by R_2, C and V_{OH}, and the time between pulses (T_2) is set by R_1, C and V_{OL}. This pulse generator can be made to have different frequencies and pulse width by selecting different capacitor value and resistor values.

Figure 66 shows another pulse generator, with separate charge and discharge paths. The capacitor is charged through R_1 and is discharged through R_2.

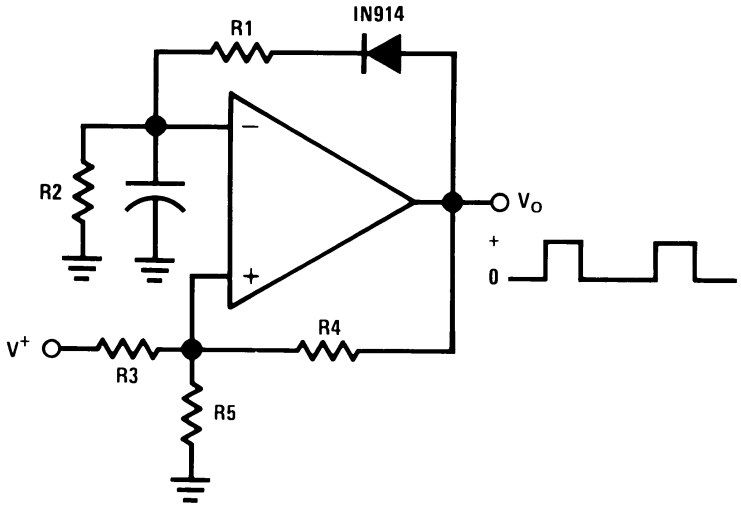

Figure 66. Pulse Generator

Figure 67 is a squarewave generator with the same path for charging and discharging the capacitor.

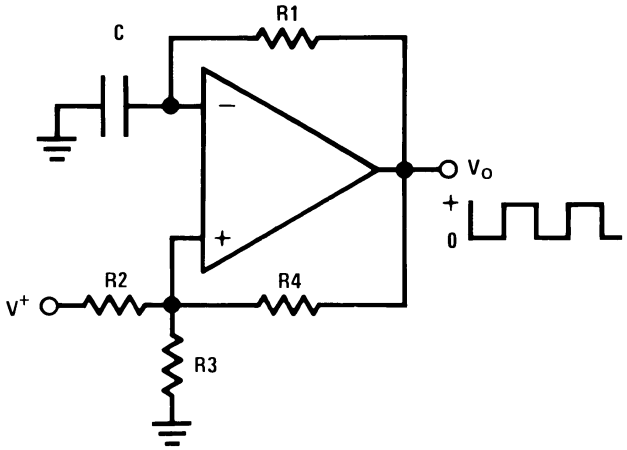

Figure 67. Squarewave Generator

CURRENT SOURCE AND SINK

The LMV321-N/LMV358-N/LMV324-N can be used in feedback loops which regulate the current in external PNP transistors to provide current sources or in external NPN transistors to provide current sinks.

Fixed Current Source

A multiple fixed current source is shown in Figure 68. A voltage (V_{REF} = 2V) is established across resistor R_3 by the voltage divider (R_3 and R_4). Negative feedback is used to cause the voltage drop across R_1 to be equal to V_{REF}. This controls the emitter current of transistor Q_1 and if we neglect the base current of Q_1 and Q_2, essentially this same current is available out of the collector of Q_1.

Large input resistors can be used to reduce current loss and a Darlington connection can be used to reduce errors due to the β of Q_1.

The resistor, R_2, can be used to scale the collector current of Q_2 either above or below the 1 mA reference value.

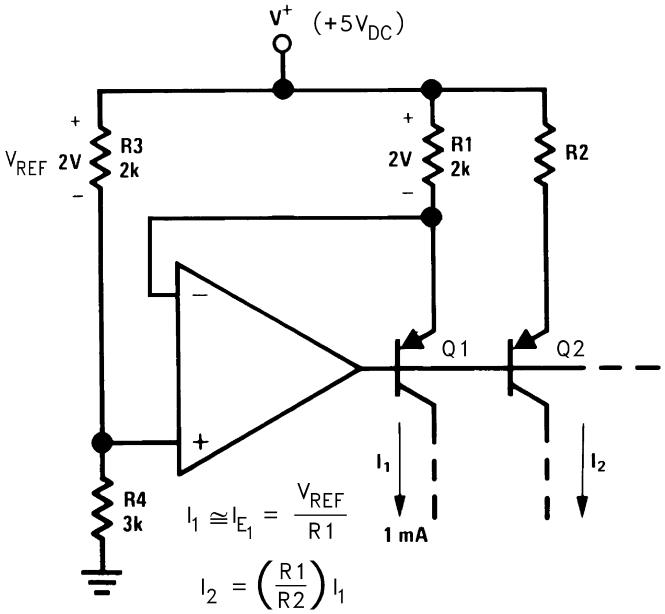

Figure 68. Fixed Current Source

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High Compliance Current Sink

A current sink circuit is shown in Figure 69. The circuit requires only one resistor (R_E) and supplies an output current which is directly proportional to this resistor value.

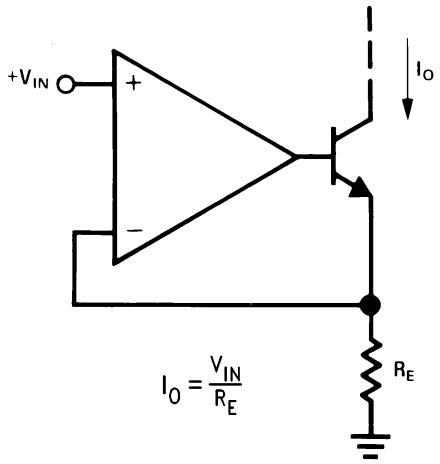

Figure 69. High Compliance Current Sink

POWER AMPLIFIER

A power amplifier is illustrated in Figure 70. This circuit can provide a higher output current because a transistor follower is added to the output of the op amp.

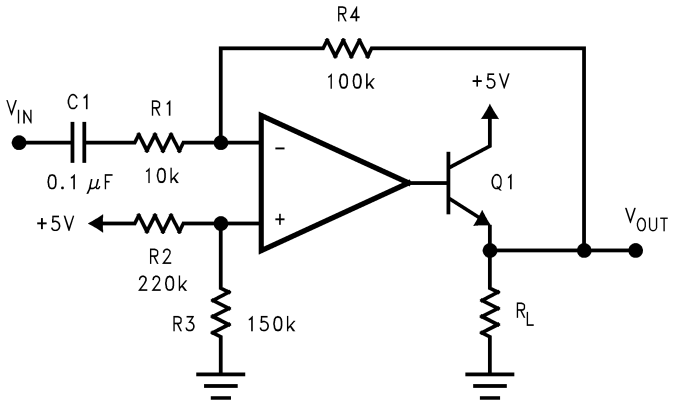

Figure 70. Power Amplifier

LED DRIVER

The LMV321-N/LMV358-N/LMV324-N can be used to drive an LED as shown in Figure 71.

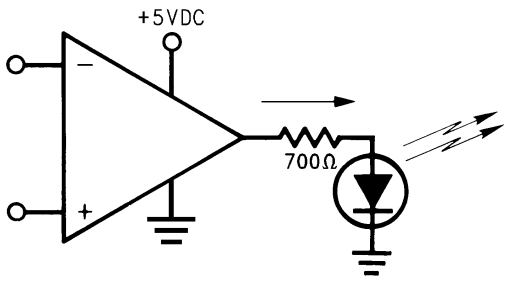

Figure 71. LED Driver

COMPARATOR WITH HYSTERESIS

The LMV321-N/LMV358-N/LMV324-N can be used as a low power comparator. Figure 72 shows a comparator with hysteresis. The hysteresis is determined by the ratio of the two resistors.

$$V_{TH+} = V_{REF}/(1+R_1/R_2)+V_{OH}/(1+R_2/R_1) \quad (30)$$

$$V_{TH-} = V_{REF}/(1+R_1/R_2)+V_{OL}/(1+R_2/R_1) \quad (31)$$

$$V_H = (V_{OH}-V_{OL})/(1+R_2/R_1) \quad (32)$$

where

V_{TH+}: Positive Threshold Voltage

V_{TH-}: Negative Threshold Voltage

V_{OH}: Output Voltage at High

V_{OL}: Output Voltage at Low

V_H: Hysteresis Voltage

Since LMV321-N/LMV358-N/LMV324-N have rail-to-rail output, the (V_{OH}–V_{OL}) is equal to V_S, which is the supply voltage.

$$V_H = V_S/(1+R_2/R_1) \quad (33)$$

The differential voltage at the input of the op amp should not exceed the specified absolute maximum ratings. For real comparators that are much faster, we recommend you use Texas Instruments's LMV331/LMV93/LMV339, which are single, dual and quad general purpose comparators for low voltage operation.

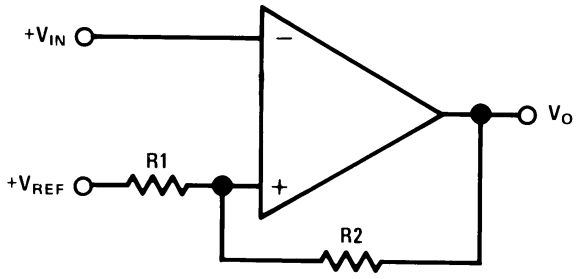

Figure 72. Comparator with Hysteresis

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REVISION HISTORY

Changes from Revision H (February 2013) to Revision I	Page
• Changed layout of National Data Sheet to TI format	28

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
LMV321M5	ACTIVE	SOT-23	DBV	5	1000	TBD	Call TI	Call TI	-40 to 85	A13	Samples
LMV321M5/NOPB	ACTIVE	SOT-23	DBV	5	1000	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	-40 to 85	A13	Samples
LMV321M5X	ACTIVE	SOT-23	DBV	5	3000	TBD	Call TI	Call TI	-40 to 85	A13	Samples
LMV321M5X/NOPB	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	-40 to 85	A13	Samples
LMV321M7	ACTIVE	SC70	DCK	5	1000	TBD	Call TI	Call TI	-40 to 85	A12	Samples
LMV321M7/NOPB	ACTIVE	SC70	DCK	5	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	A12	Samples
LMV321M7X	ACTIVE	SC70	DCK	5	3000	TBD	Call TI	Call TI	-40 to 85	A12	Samples
LMV321M7X/NOPB	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	A12	Samples
LMV321Q1M5/NOPB	ACTIVE	SOT-23	DBV	5	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	AYA	Samples
LMV321Q1M5X/NOPB	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	AYA	Samples
LMV321Q3M5/NOPB	ACTIVE	SOT-23	DBV	5	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	AZA	Samples
LMV321Q3M5X/NOPB	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	AZA	Samples
LMV324M	ACTIVE	SOIC	D	14	55	TBD	Call TI	Call TI	-40 to 85	LMV324M	Samples
LMV324M/NOPB	ACTIVE	SOIC	D	14	55	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV324M	Samples
LMV324MT	ACTIVE	TSSOP	PW	14	94	TBD	Call TI	Call TI	-40 to 85	LMV324 MT	Samples
LMV324MT/NOPB	ACTIVE	TSSOP	PW	14	94	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV324 MT	Samples
LMV324MTX	ACTIVE	TSSOP	PW	14	2500	TBD	Call TI	Call TI	-40 to 85	LMV324 MT	Samples
LMV324MTX/NOPB	ACTIVE	TSSOP	PW	14	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV324 MT	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
LMV324MX	ACTIVE	SOIC	D	14	2500	TBD	Call TI	Call TI	-40 to 85	LMV324M	Samples
LMV324MX/NOPB	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV324M	Samples
LMV324Q1MA/NOPB	ACTIVE	SOIC	D	14	55	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LMV324Q1 MA	Samples
LMV324Q1MAX/NOPB	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LMV324Q1 MA	Samples
LMV324Q1MT/NOPB	ACTIVE	TSSOP	PW	14	94	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LMV324 Q1MT	Samples
LMV324Q1MTX/NOPB	ACTIVE	TSSOP	PW	14	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LMV324 Q1MT	Samples
LMV324Q3MA/NOPB	ACTIVE	SOIC	D	14	55	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV324Q3 MA	Samples
LMV324Q3MAX/NOPB	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV324Q3 MA	Samples
LMV324Q3MT/NOPB	ACTIVE	TSSOP	PW	14	94	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV324 Q3MT	Samples
LMV324Q3MTX/NOPB	ACTIVE	TSSOP	PW	14	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV324 Q3MT	Samples
LMV358M	ACTIVE	SOIC	D	8	95	TBD	Call TI	Call TI	-40 to 85	LMV 358M	Samples
LMV358M/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV 358M	Samples
LMV358MM	ACTIVE	VSSOP	DGK	8	1000	TBD	Call TI	Call TI	-40 to 85	V358	Samples
LMV358MM/NOPB	ACTIVE	VSSOP	DGK	8	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	V358	Samples
LMV358MMX	ACTIVE	VSSOP	DGK	8	3500	TBD	Call TI	Call TI	-40 to 85	V358	Samples
LMV358MMX/NOPB	ACTIVE	VSSOP	DGK	8	3500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	V358	Samples
LMV358MX	ACTIVE	SOIC	D	8	2500	TBD	Call TI	Call TI	-40 to 85	LMV 358M	Samples
LMV358MX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV 358M	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
LMV358Q1MA/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LMV35 8Q1MA	Samples
LMV358Q1MAX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LMV35 8Q1MA	Samples
LMV358Q1MM/NOPB	ACTIVE	VSSOP	DGK	8	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	AFAA	Samples
LMV358Q1MMX/NOPB	ACTIVE	VSSOP	DGK	8	3500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	AFAA	Samples
LMV358Q3MA/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV35 8Q3MA	Samples
LMV358Q3MAX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LMV35 8Q3MA	Samples
LMV358Q3MM/NOPB	ACTIVE	VSSOP	DGK	8	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	AHAA	Samples
LMV358Q3MMX/NOPB	ACTIVE	VSSOP	DGK	8	3500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	AHAA	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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OTHER QUALIFIED VERSIONS OF LMV321-N, LMV321-N-Q1, LMV324-N, LMV324-N-Q1, LMV358-N, LMV358-N-Q1 :

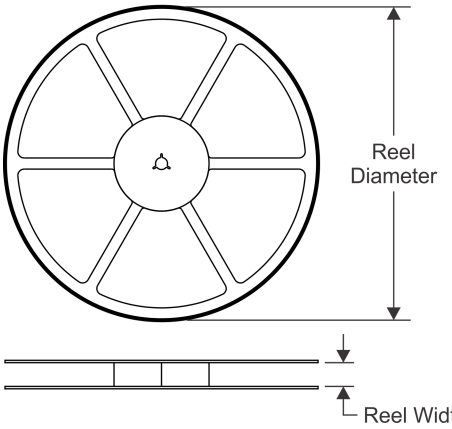
- Catalog: LMV321-N, LMV324-N, LMV358-N
- Automotive: LMV321-N-Q1, LMV324-N-Q1, LMV358-N-Q1

NOTE: Qualified Version Definitions:

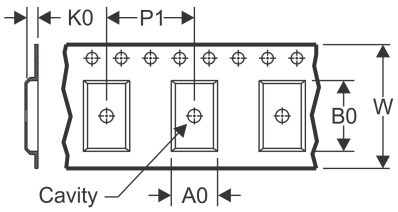
- Catalog - TI's standard catalog product
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

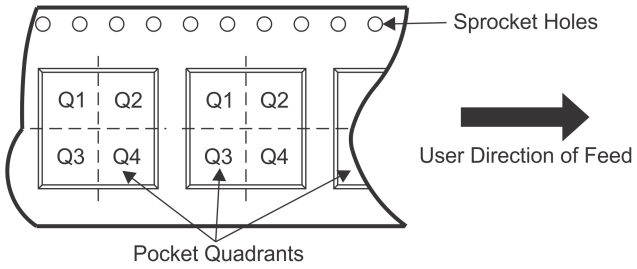


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

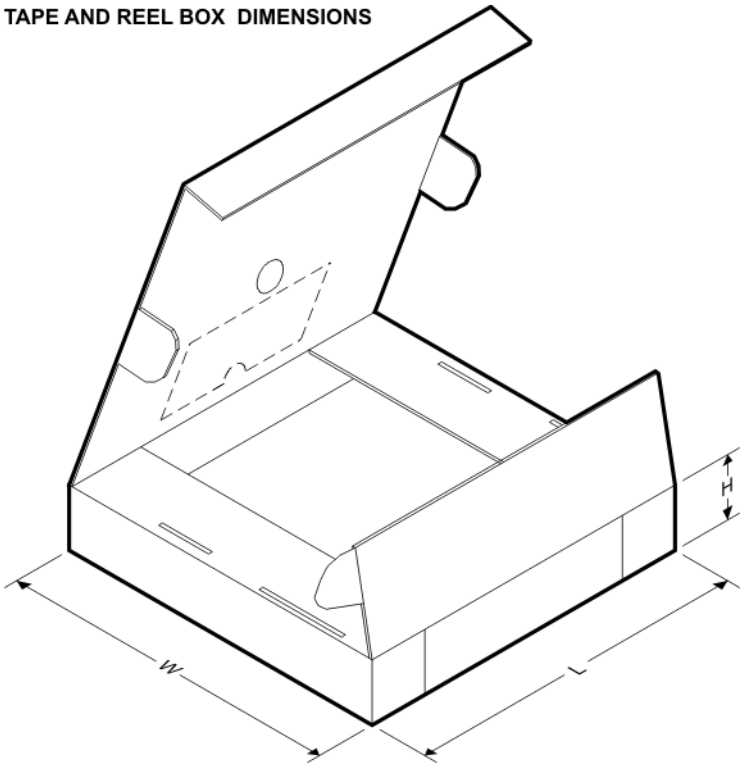


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMV321M5	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321M5/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321M5X	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321M5X/NOPB	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321M7	SC70	DCK	5	1000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3
LMV321M7/NOPB	SC70	DCK	5	1000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3
LMV321M7X	SC70	DCK	5	3000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3
LMV321M7X/NOPB	SC70	DCK	5	3000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3
LMV321Q1M5/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321Q1M5X/NOPB	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321Q3M5/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321Q3M5X/NOPB	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV324MTX	TSSOP	PW	14	2500	330.0	12.4	6.95	8.3	1.6	8.0	12.0	Q1
LMV324MTX/NOPB	TSSOP	PW	14	2500	330.0	12.4	6.95	8.3	1.6	8.0	12.0	Q1
LMV324MX	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1
LMV324MX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1
LMV324Q1MAX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1
LMV324Q3MAX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMV358MM	VSSOP	DGK	8	1000	178.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358MM/NOPB	VSSOP	DGK	8	1000	178.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358MMX	VSSOP	DGK	8	3500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358MMX/NOPB	VSSOP	DGK	8	3500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358MX	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMV358MX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMV358Q1MAX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMV358Q1MM/NOPB	VSSOP	DGK	8	1000	178.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358Q1MMX/NOPB	VSSOP	DGK	8	3500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358Q3MAX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMV358Q3MM/NOPB	VSSOP	DGK	8	1000	178.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358Q3MMX/NOPB	VSSOP	DGK	8	3500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

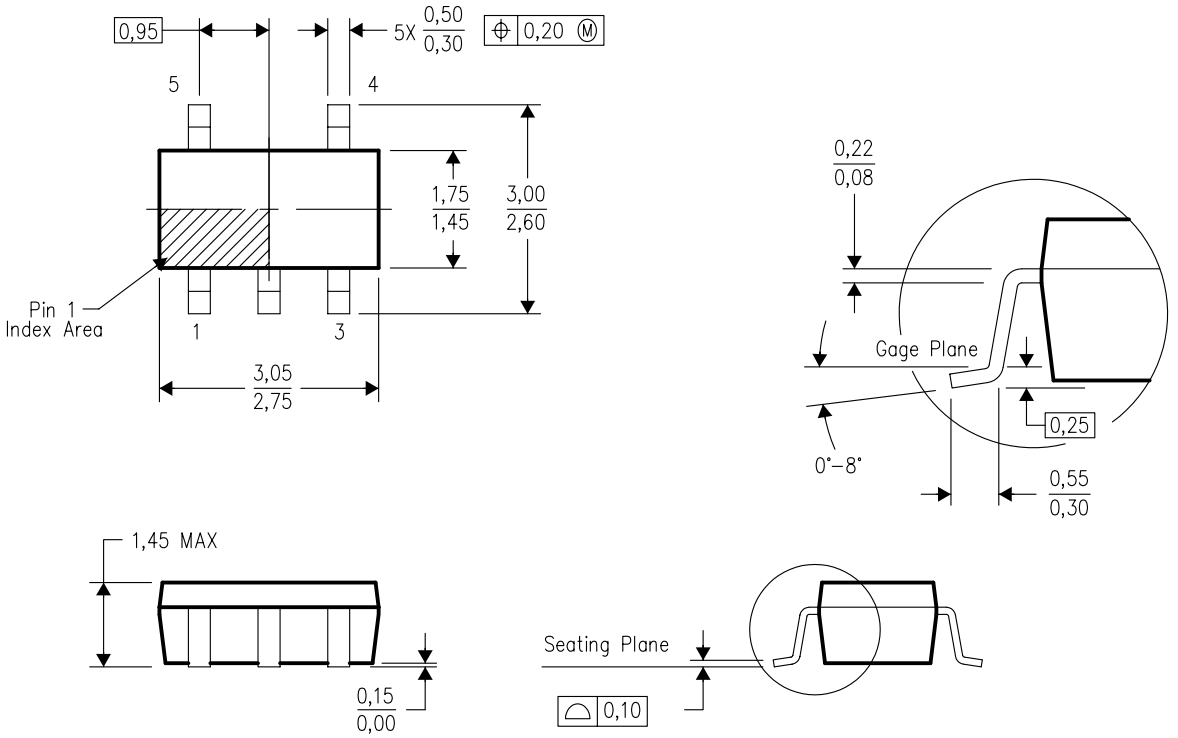


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMV321M5	SOT-23	DBV	5	1000	210.0	185.0	35.0
LMV321M5/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LMV321M5X	SOT-23	DBV	5	3000	210.0	185.0	35.0
LMV321M5X/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0
LMV321M7	SC70	DCK	5	1000	210.0	185.0	35.0

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMV321M7/NOPB	SC70	DCK	5	1000	210.0	185.0	35.0
LMV321M7X	SC70	DCK	5	3000	210.0	185.0	35.0
LMV321M7X/NOPB	SC70	DCK	5	3000	210.0	185.0	35.0
LMV321Q1M5/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LMV321Q1M5X/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0
LMV321Q3M5/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LMV321Q3M5X/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0
LMV324MTX	TSSOP	PW	14	2500	367.0	367.0	35.0
LMV324MTX/NOPB	TSSOP	PW	14	2500	367.0	367.0	35.0
LMV324MX	SOIC	D	14	2500	367.0	367.0	35.0
LMV324MX/NOPB	SOIC	D	14	2500	367.0	367.0	35.0
LMV324Q1MAX/NOPB	SOIC	D	14	2500	349.0	337.0	45.0
LMV324Q3MAX/NOPB	SOIC	D	14	2500	349.0	337.0	45.0
LMV358MM	VSSOP	DGK	8	1000	210.0	185.0	35.0
LMV358MM/NOPB	VSSOP	DGK	8	1000	210.0	185.0	35.0
LMV358MMX	VSSOP	DGK	8	3500	367.0	367.0	35.0
LMV358MMX/NOPB	VSSOP	DGK	8	3500	367.0	367.0	35.0
LMV358MX	SOIC	D	8	2500	367.0	367.0	35.0
LMV358MX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LMV358Q1MAX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LMV358Q1MM/NOPB	VSSOP	DGK	8	1000	210.0	185.0	35.0
LMV358Q1MMX/NOPB	VSSOP	DGK	8	3500	367.0	367.0	35.0
LMV358Q3MAX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LMV358Q3MM/NOPB	VSSOP	DGK	8	1000	210.0	185.0	35.0
LMV358Q3MMX/NOPB	VSSOP	DGK	8	3500	367.0	367.0	35.0

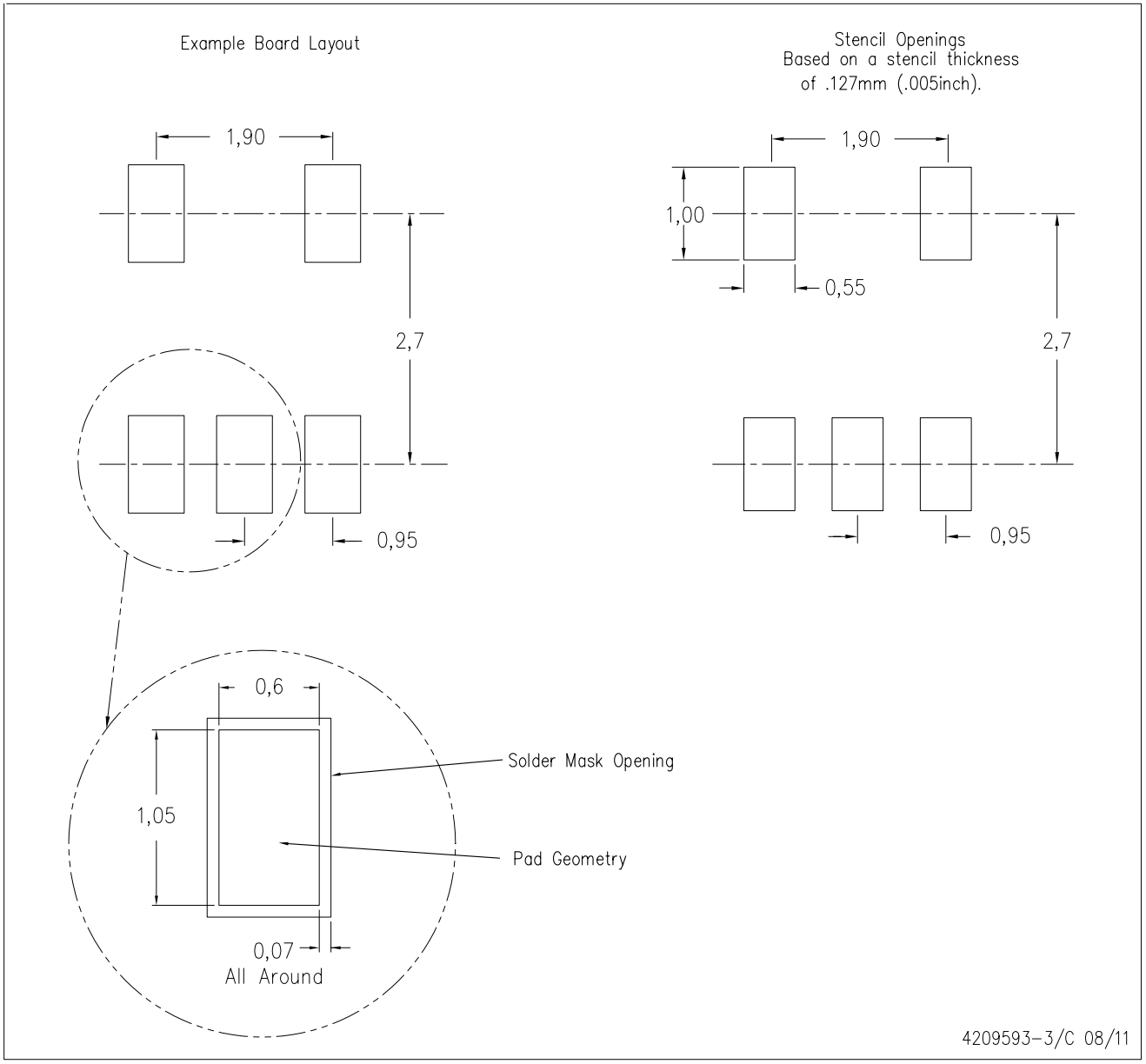
DBV (R–PDSO–G5) PLASTIC SMALL–OUTLINE PACKAGE



4073253–4/K 03/2006

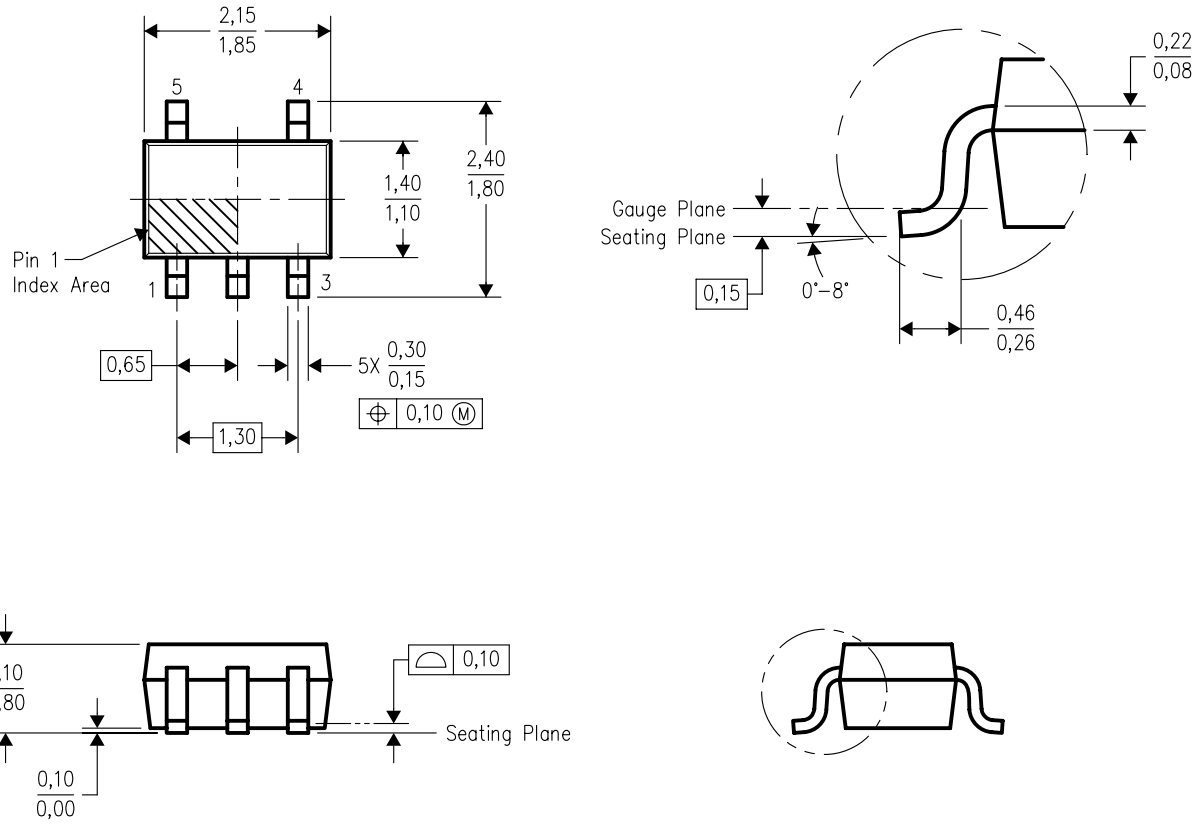
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–178 Variation AA.

DBV (R–PDSO–G5) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
D. Publication IPC–7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.

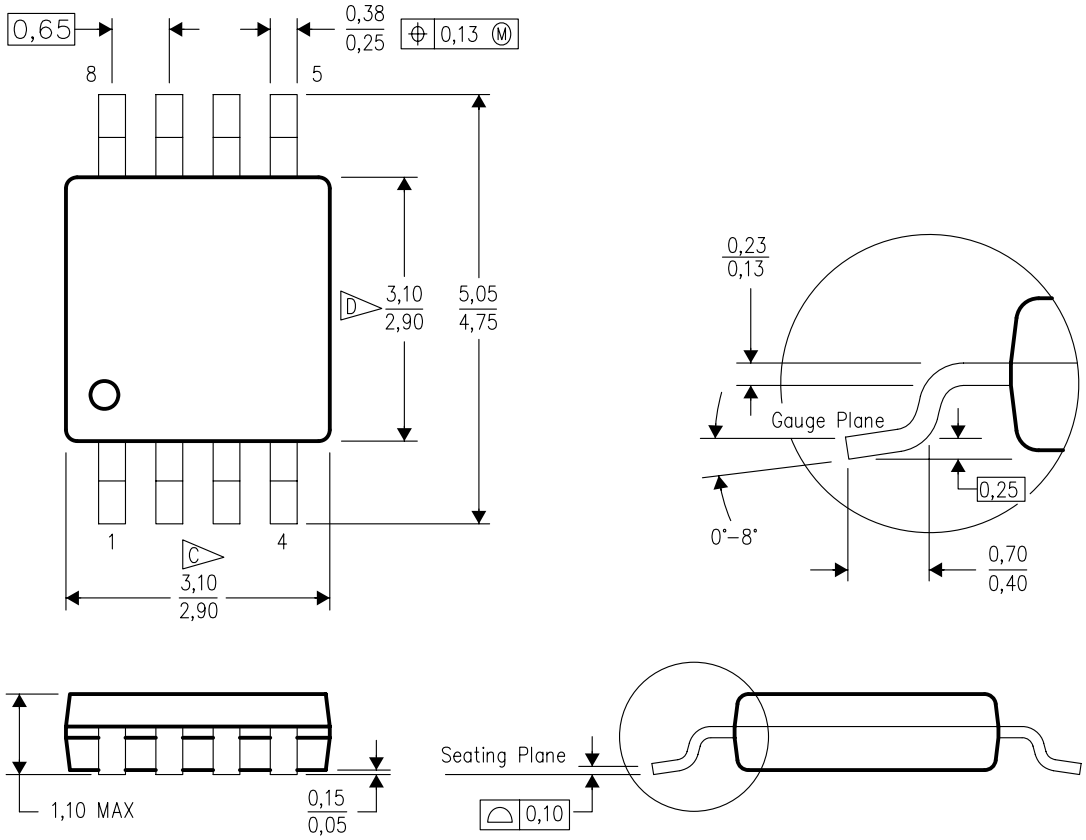
DCK (R–PDSO–G5) PLASTIC SMALL–OUTLINE PACKAGE



4093553–3/G 01/2007

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–203 variation AA.

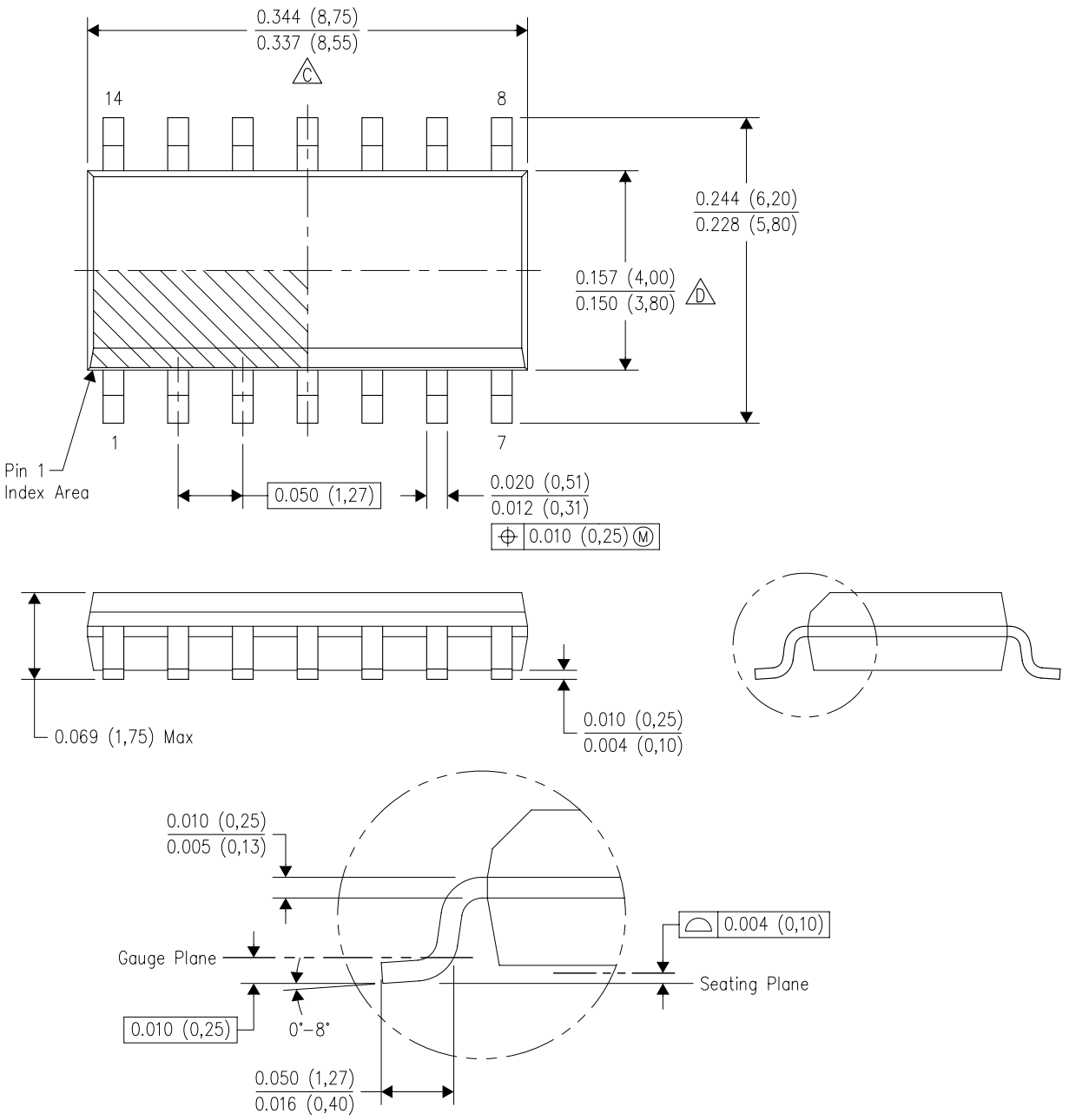
DGK (S–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE



4073329/E 05/06

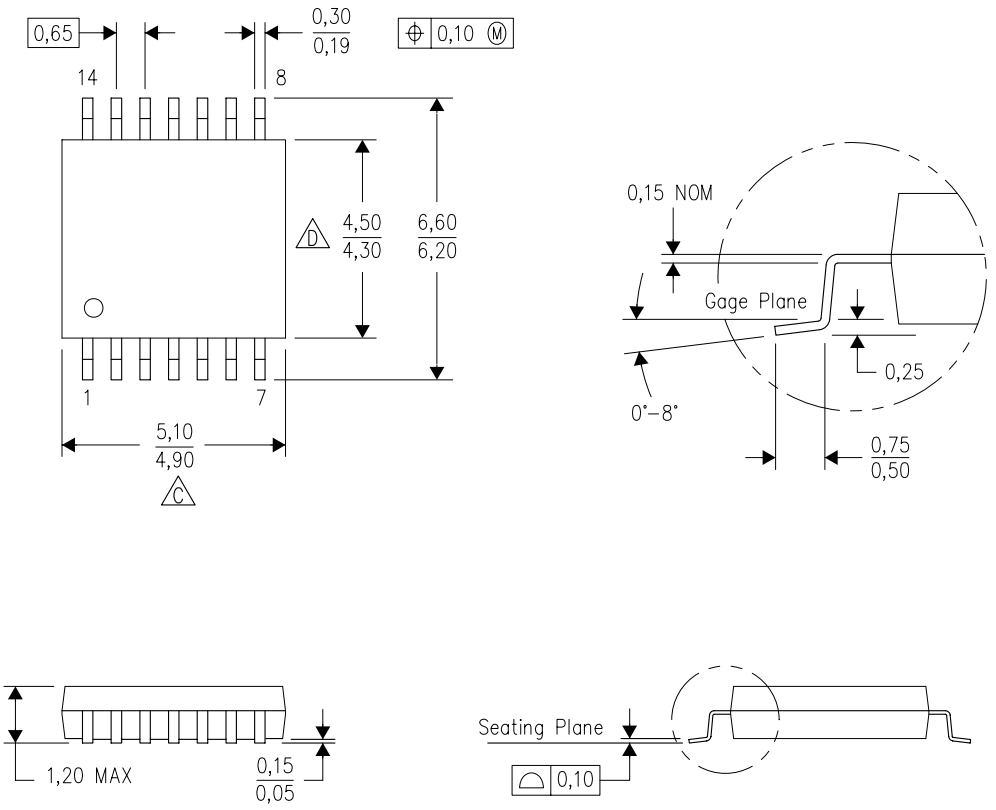
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
E. Falls within JEDEC MO–187 variation AA, except interlead flash.

D (R–PDSO–G14) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AB.

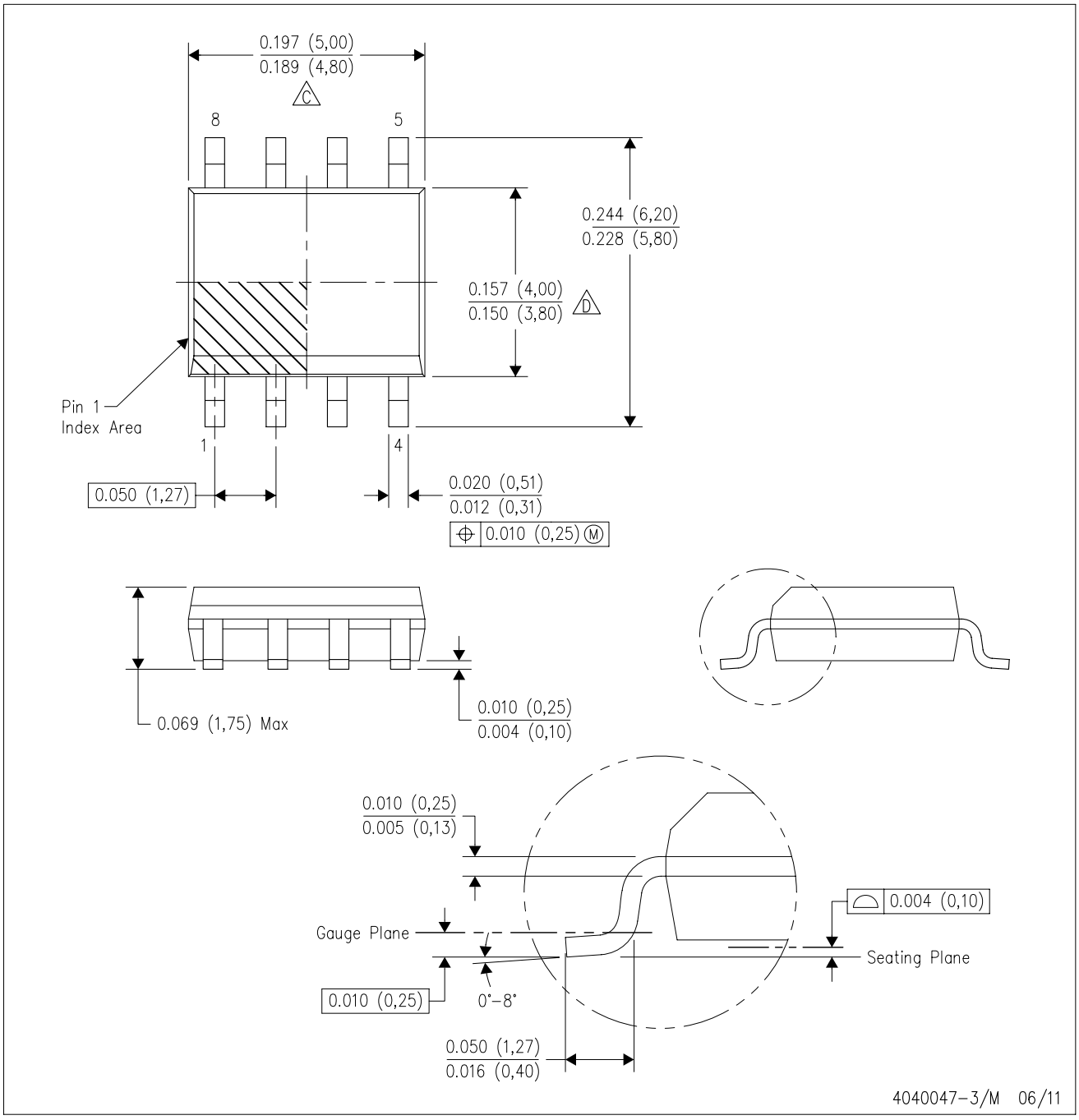
PW (R–PDSO–G14) PLASTIC SMALL OUTLINE



4040064–3/G 02/11

NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO–153

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AA.

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